



**IChF**

Institute of Physical Chemistry PAS

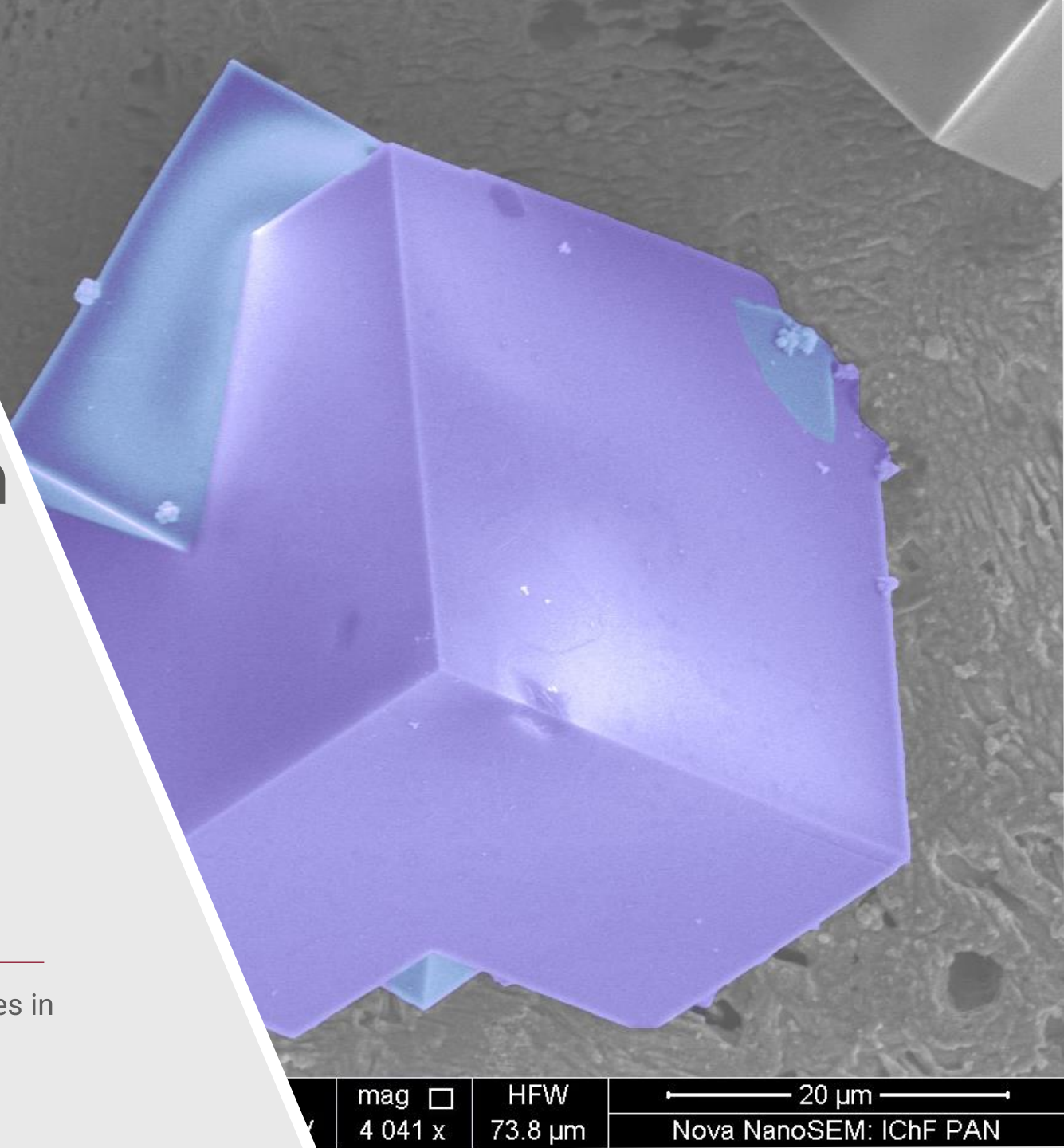
# A practical introduction to scanning electron microscopy

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Charge Transfer Processes in  
Hydrodynamic systems



mag ☐  
4 041 x

HFV  
73.8 μm

20 μm  
Nova NanoSEM: IChF PAN

# Practical information

4 hours lectures

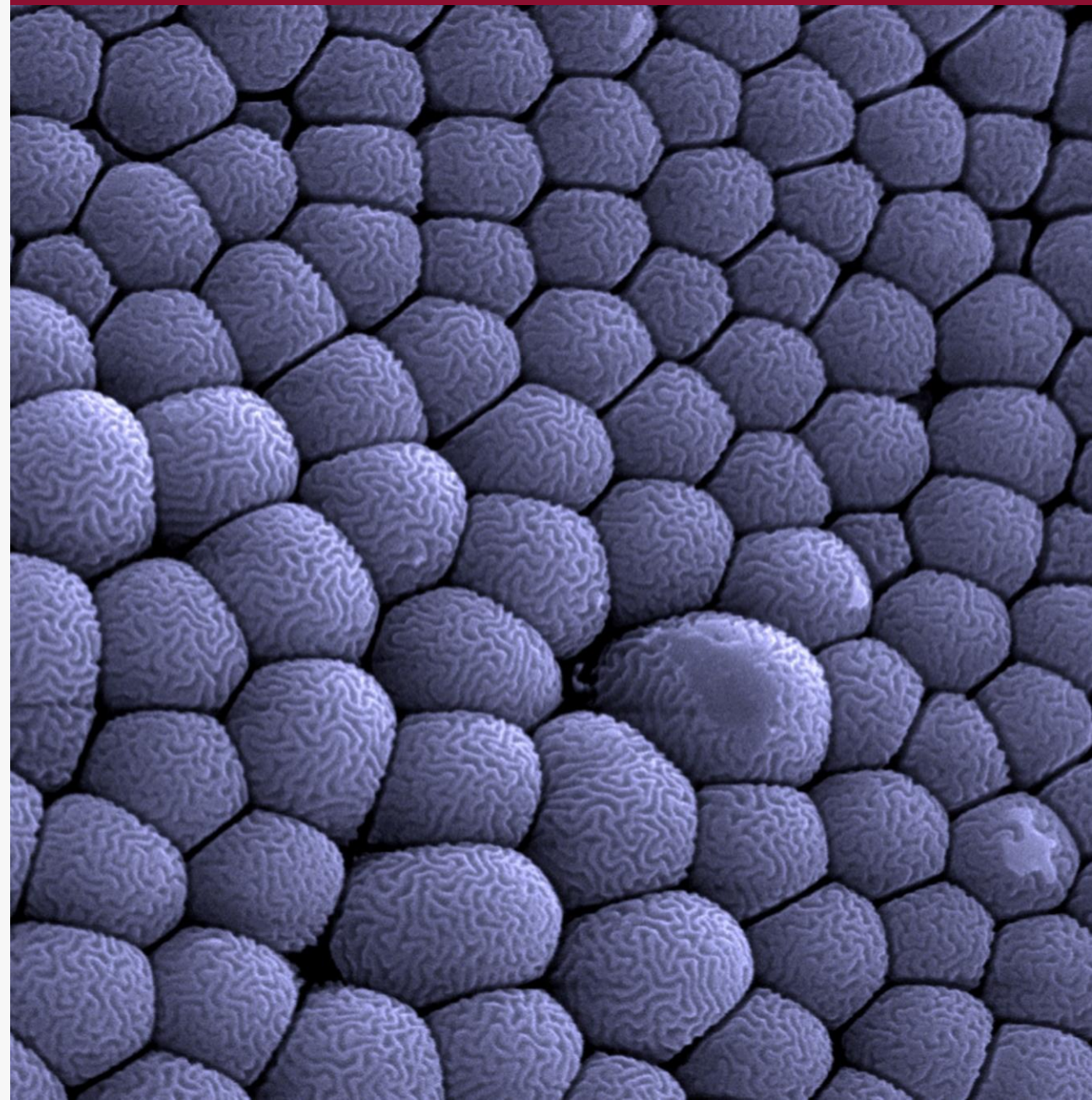
4 hour practicals (groups of 3)

Exam: Measure “mystery sample”  
Analyse images (size, composition)  
Hand in report

Info on [www.charge-transfer.pl/sem-course](http://www.charge-transfer.pl/sem-course)

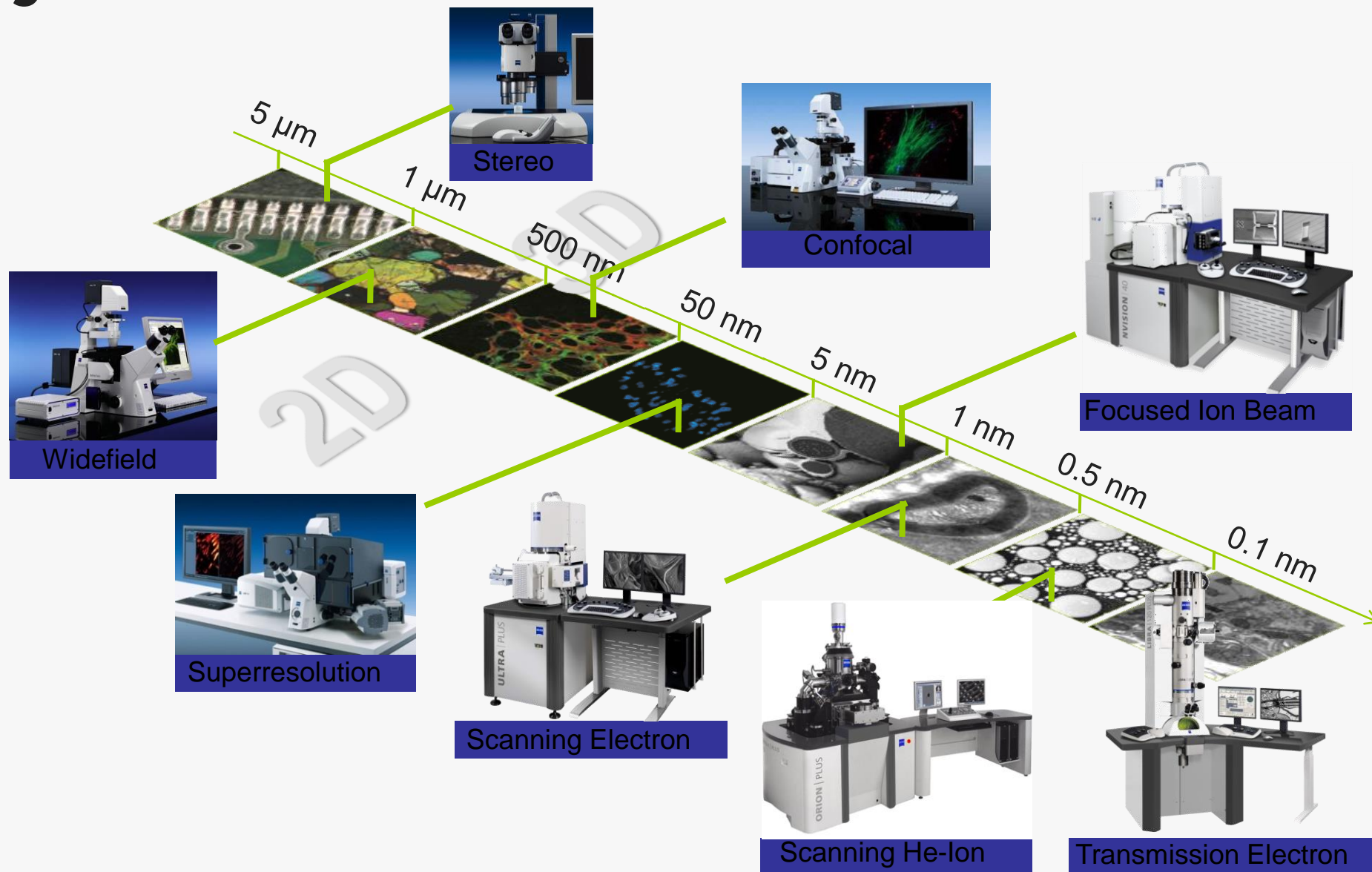
## Content

- Basic principles
- Electron-matter interaction
- Settings and limitations
- Different detection modes
- Our system
- Sample preparation
- EDX / WDX





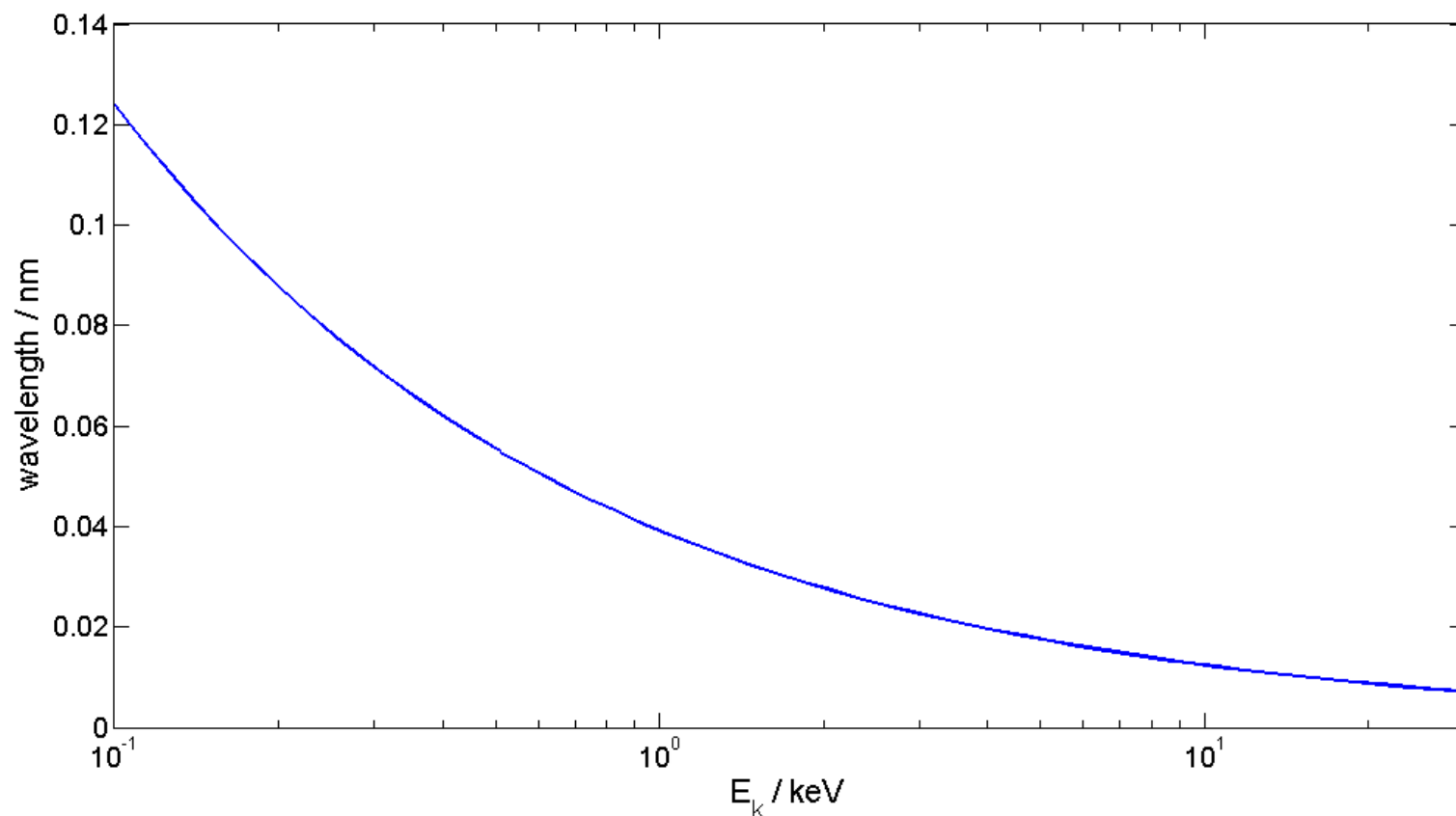
# Why SEM?



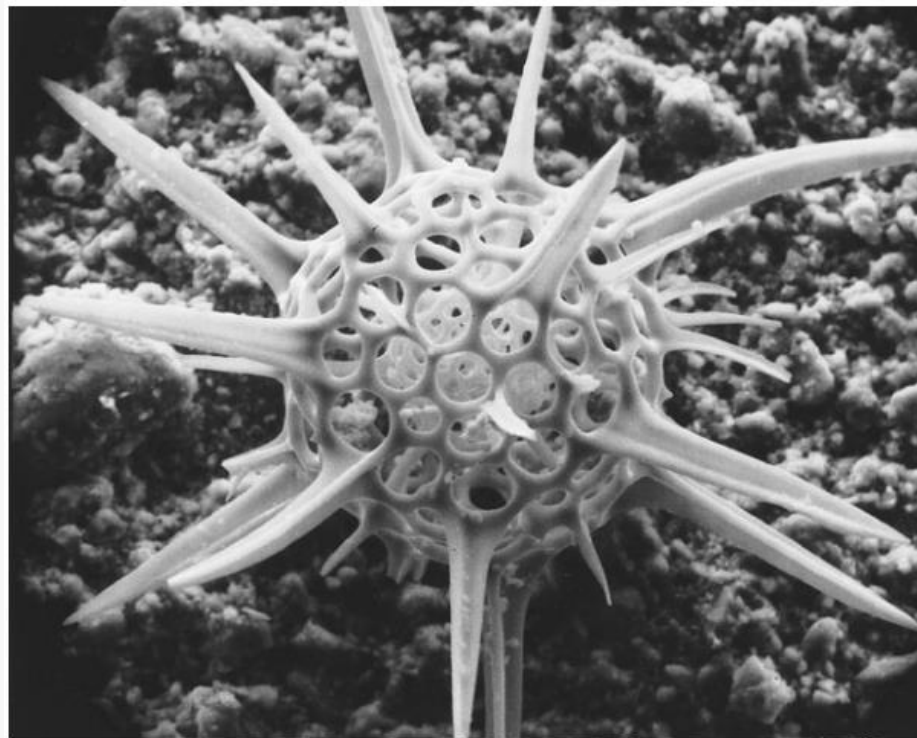
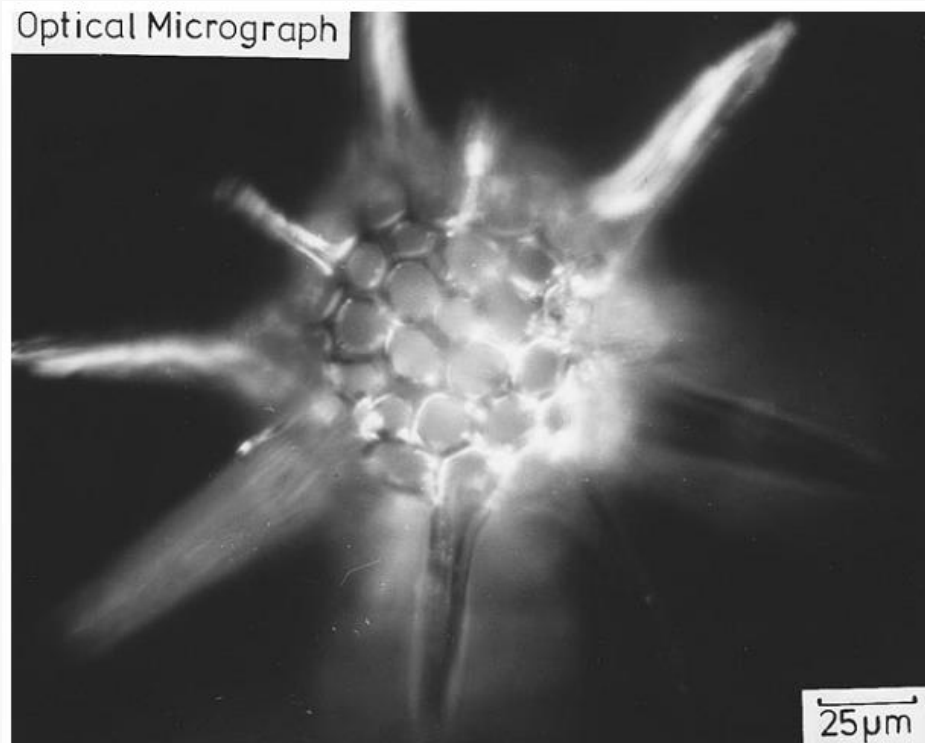
# Why SEM?

de Broglie wave-length

$$\lambda = \frac{h}{\sqrt{2mE_{kin}}} \approx \frac{1.23}{\sqrt{E_{kin}}} \text{ nm}$$



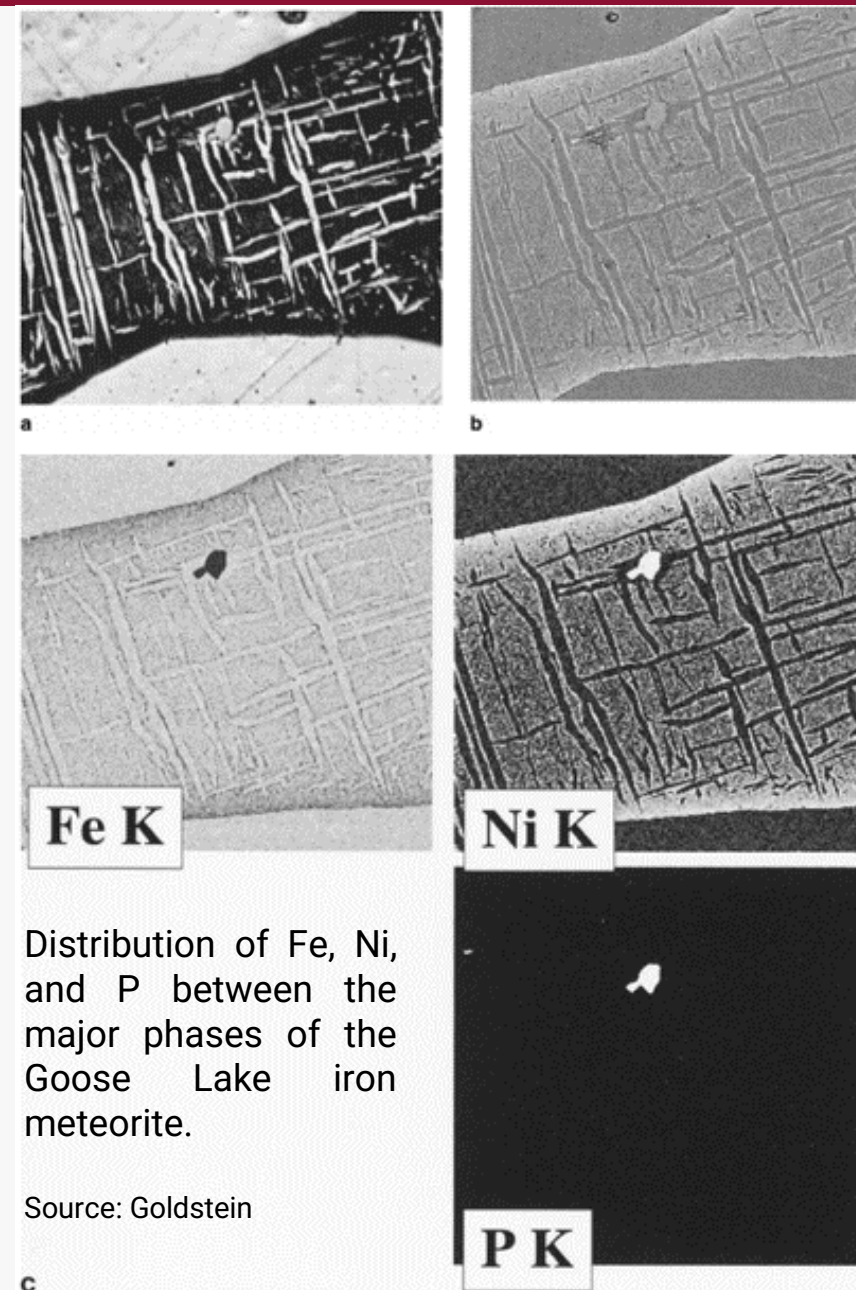
# Why SEM?



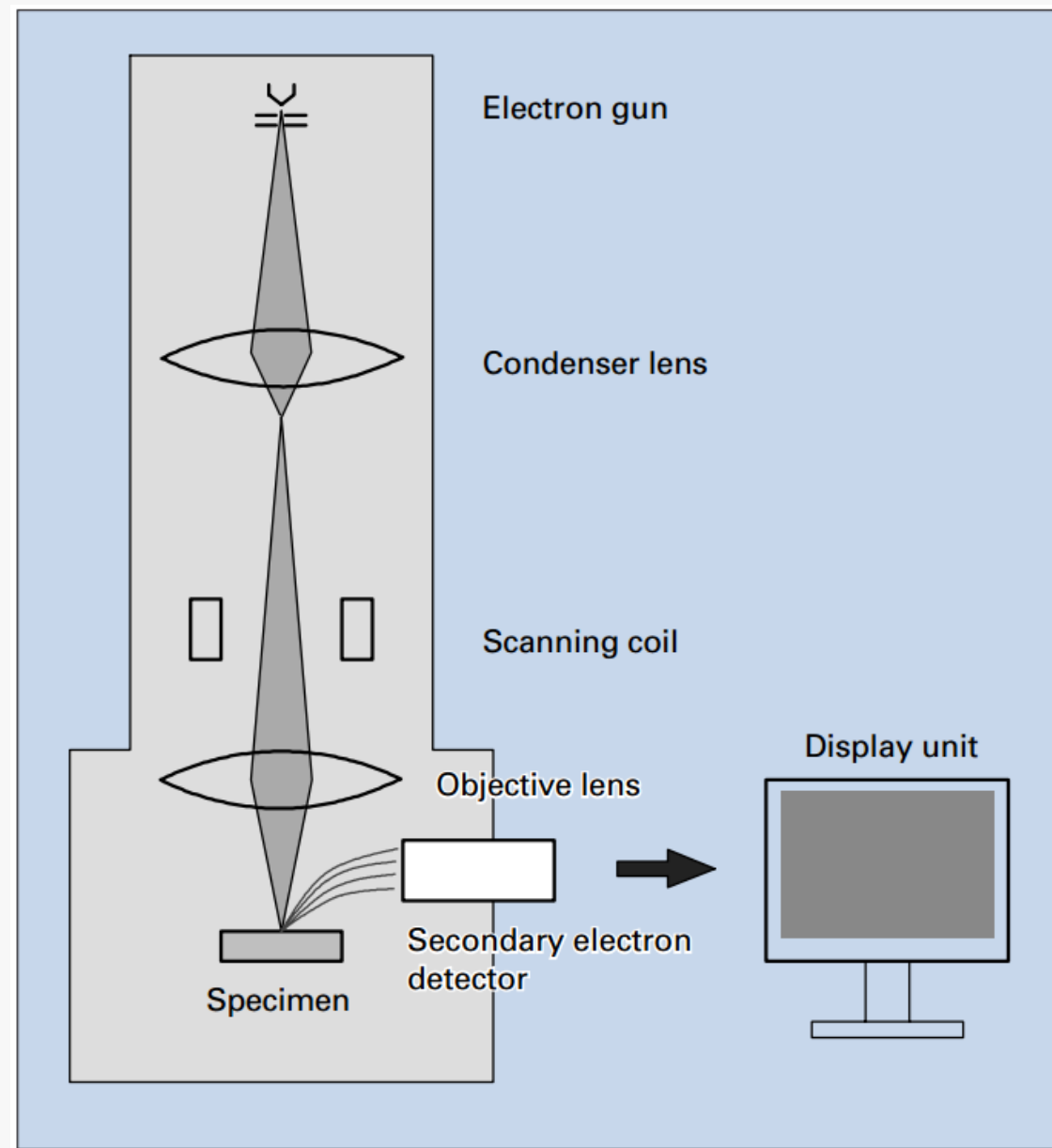
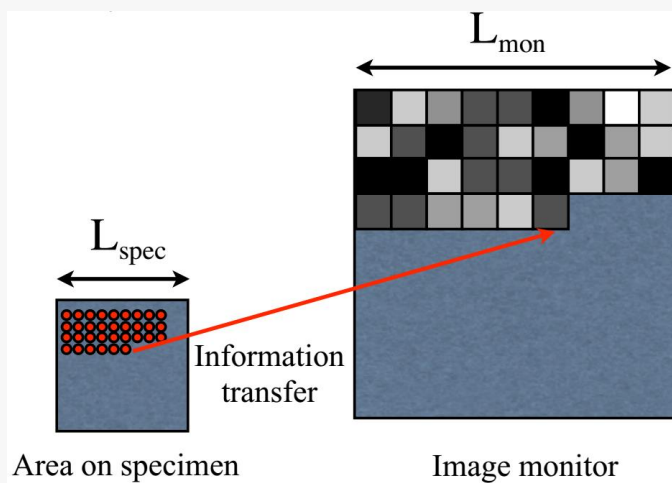
Optical and SEM micrograph of the radiolarian *Trochodiscus longispinus*

# Why SEM?

- Versatile
- Topography
- Elemental information
- Crystallinity
- Fast
- Non-destructive (mostly)
- Easy (mostly)



# Working principle



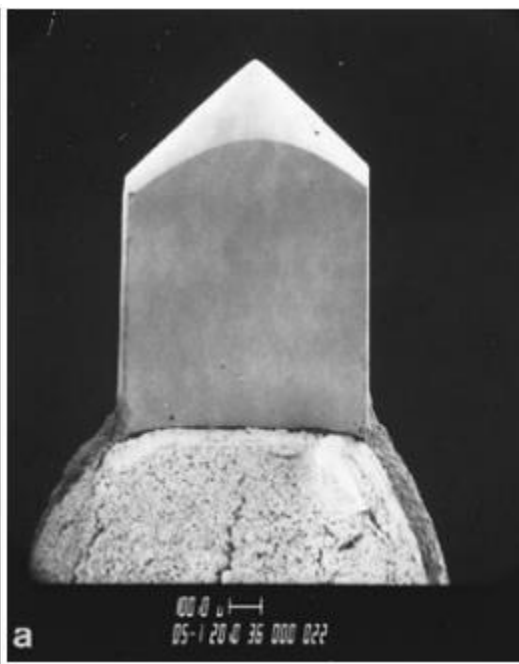


# Electron gun

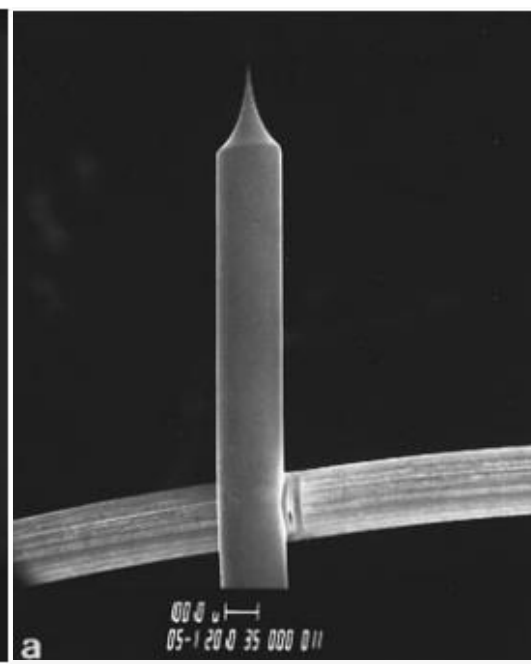
|  | TE gun                |                  | FE gun        | SE gun       |
|--|-----------------------|------------------|---------------|--------------|
|  | Tungsten              | LaB <sub>6</sub> |               |              |
| Electron-source size                             | 15 ~ 20 $\mu\text{m}$ | 10 $\mu\text{m}$ | 5 ~ 10nm      | 15 ~ 20nm    |
| Brightness ( $\text{Acm}^{-2} \text{rad}^{-2}$ ) | $10^5$                | $10^6$           | $10^8$        | $10^8$       |
| Energy spread (eV)                               | 3 ~ 4                 | 2 ~ 3            | 0.3           | 0.7 ~ 1      |
| Lifetime   | 50 h                  | 500 h            | Several years | 1 to 2 years |
| Cathode temperature (K)                          | 2800                  | 1900             | 300           | 1800         |
| Current fluctuation (per hour)                   | <1%                   | <2%              | >10%          | <1%          |



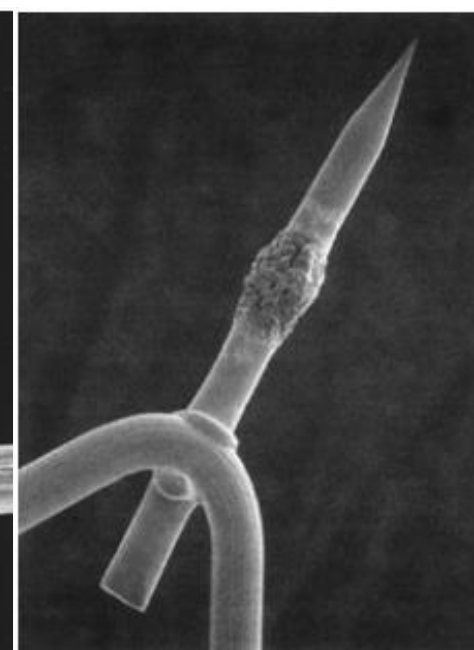
Tungsten wire thermionic emitter



Lanthanum hexaboride thermionic emitter



Tungsten singly-crystal cold field emission tip



Tungsten/ZrO<sub>2</sub> Schottky field emission tip



# Electron lenses

In SEM magnetic lenses are used.

Cylindrically symmetric

“Soft magnetic” shell

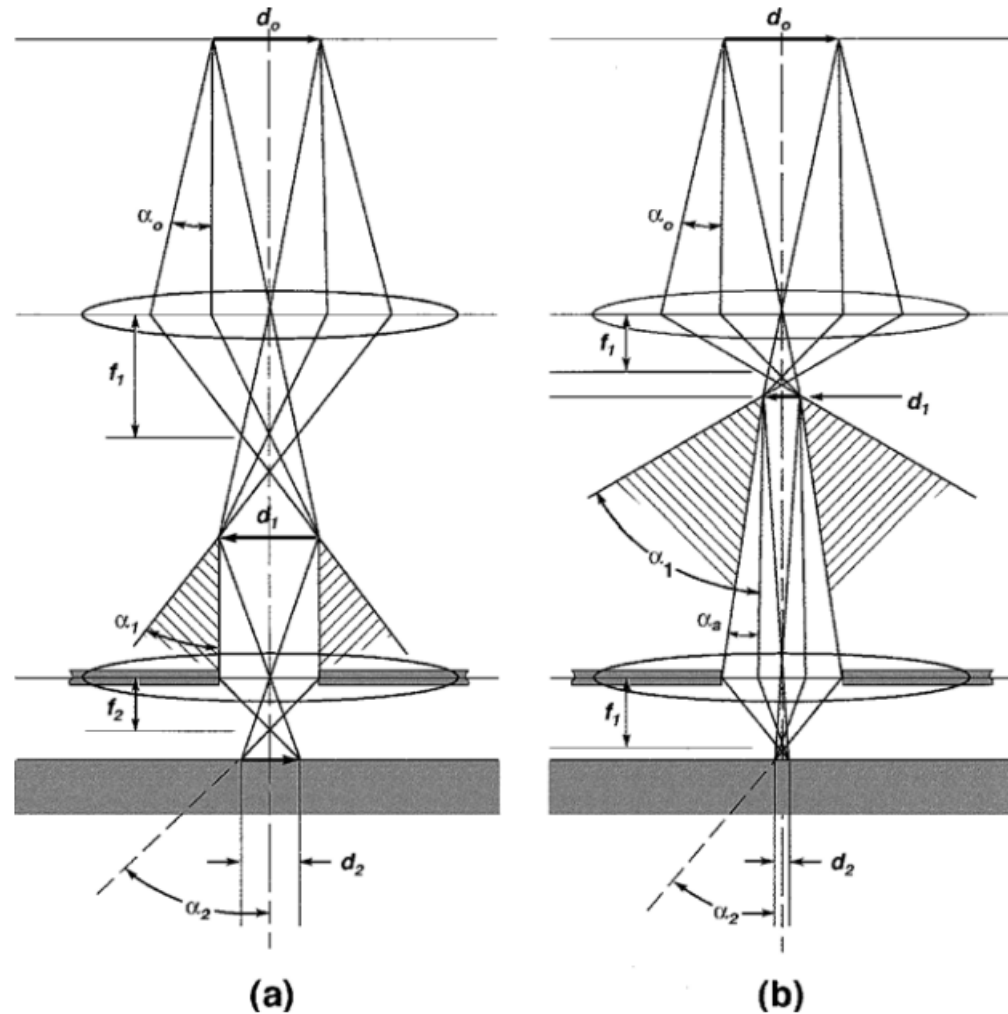
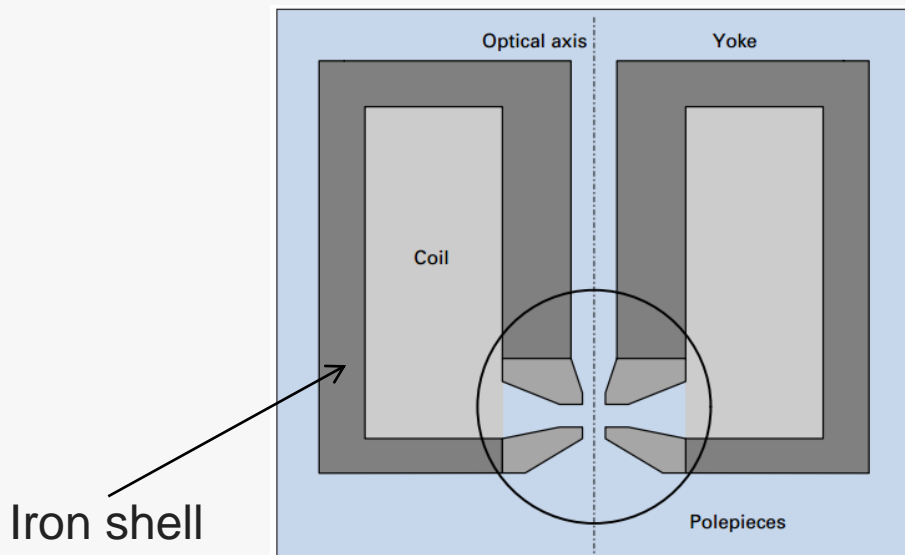
Field leaks out at narrow gap.

Only the pole pieces need to be very accurately fabricated

Focal length of the lens can be changed

$$f \approx V_0 / (NI)^2$$

Beam is twisted through the lens



**Figure 2.20.** Effect of condenser lens strength in a two-lens lens system. (a) Weak condenser lens, (b) strong condenser lens.

Weak lens ('large spot')

→ Higher current

→ Lower resolution

# Objective lens

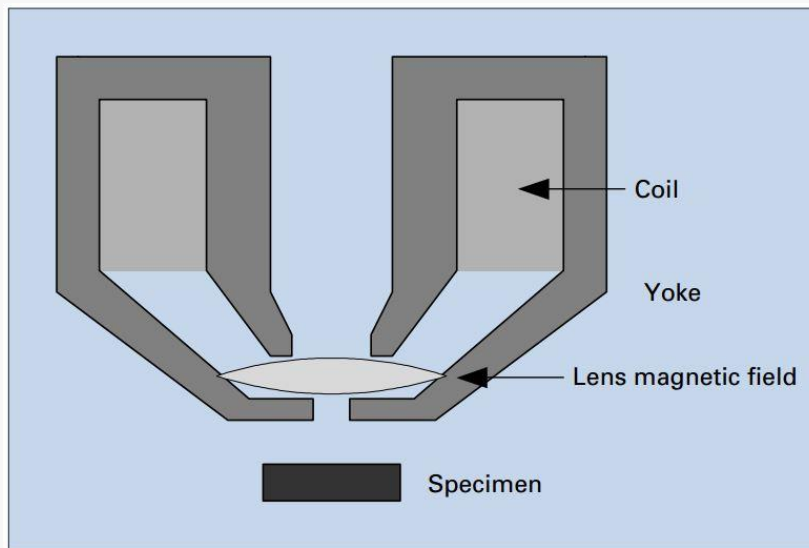


Fig. 34 Construction of the conventional objective lens.

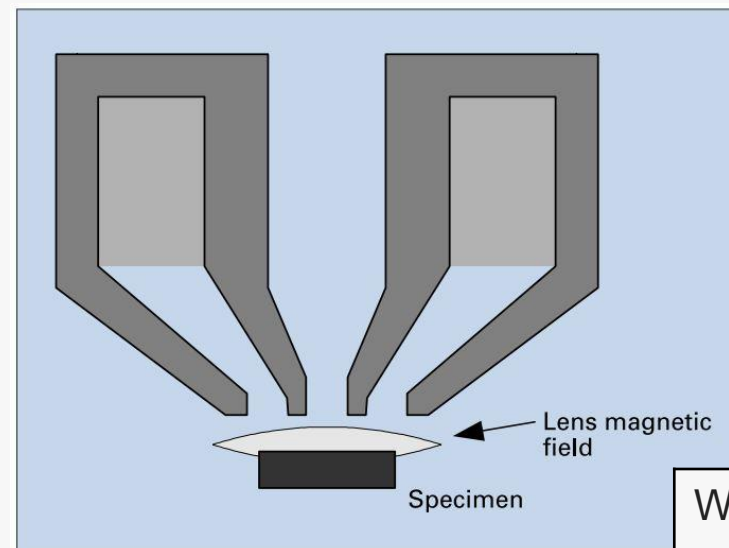


Fig. 36 Construction of the semi-in-lens objective lens.

snorkel  
immersion

Snorkel / immersion:

- Higher resolution
- Lower max field of view (min ca 1500x)
- Only in-lens detector
- Restriction on magnetic materials
- Limit on usable voltages

| WD / mm | $E_{\max}$ / kV |
|---------|-----------------|
| 1       | 1.2             |
| 2       | 3.5             |
| 3       | 7               |
| 4       | 12              |
| 5       | 18              |
| 6       | 24              |
| 7       | 30              |

# Resolution limit

Resolution is given by probe diameter (size of electron beam)

• Gaussian beam diameter (no aberration)

$$d_G = \sqrt{\frac{4i_p}{\beta\pi^2\alpha_p^2}}$$

• Diffraction in aperture

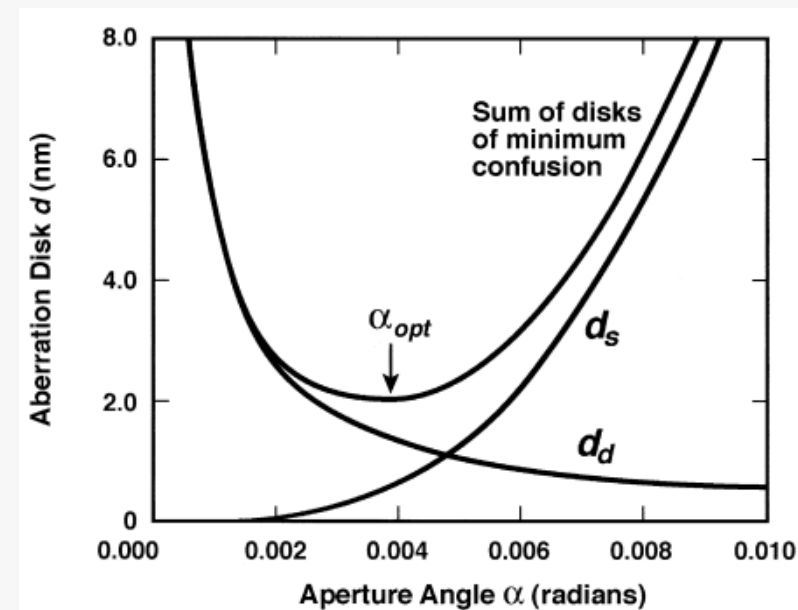
• Spherical aberration

$$d_s = \frac{1}{2}C_s\alpha^3,$$

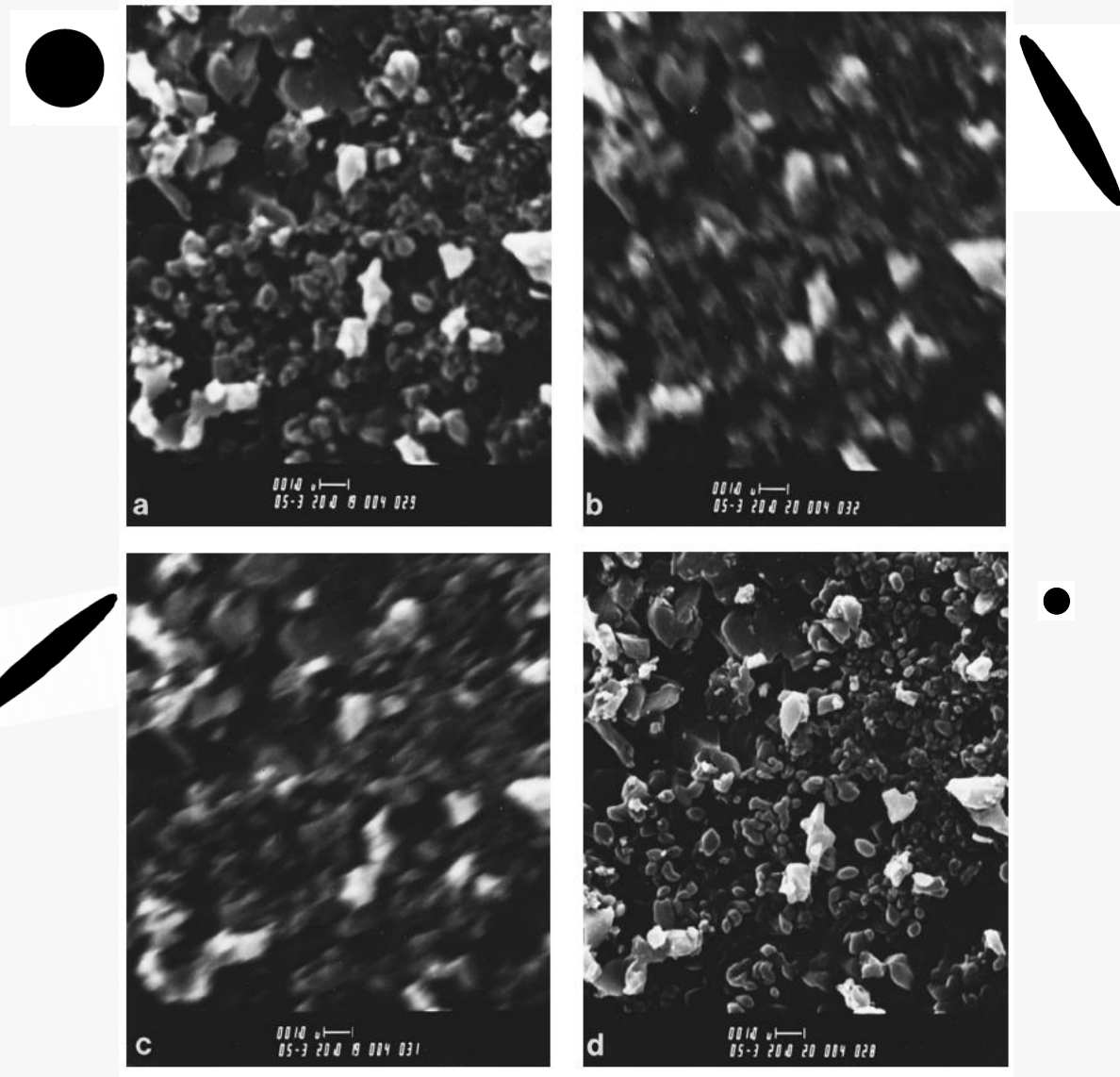
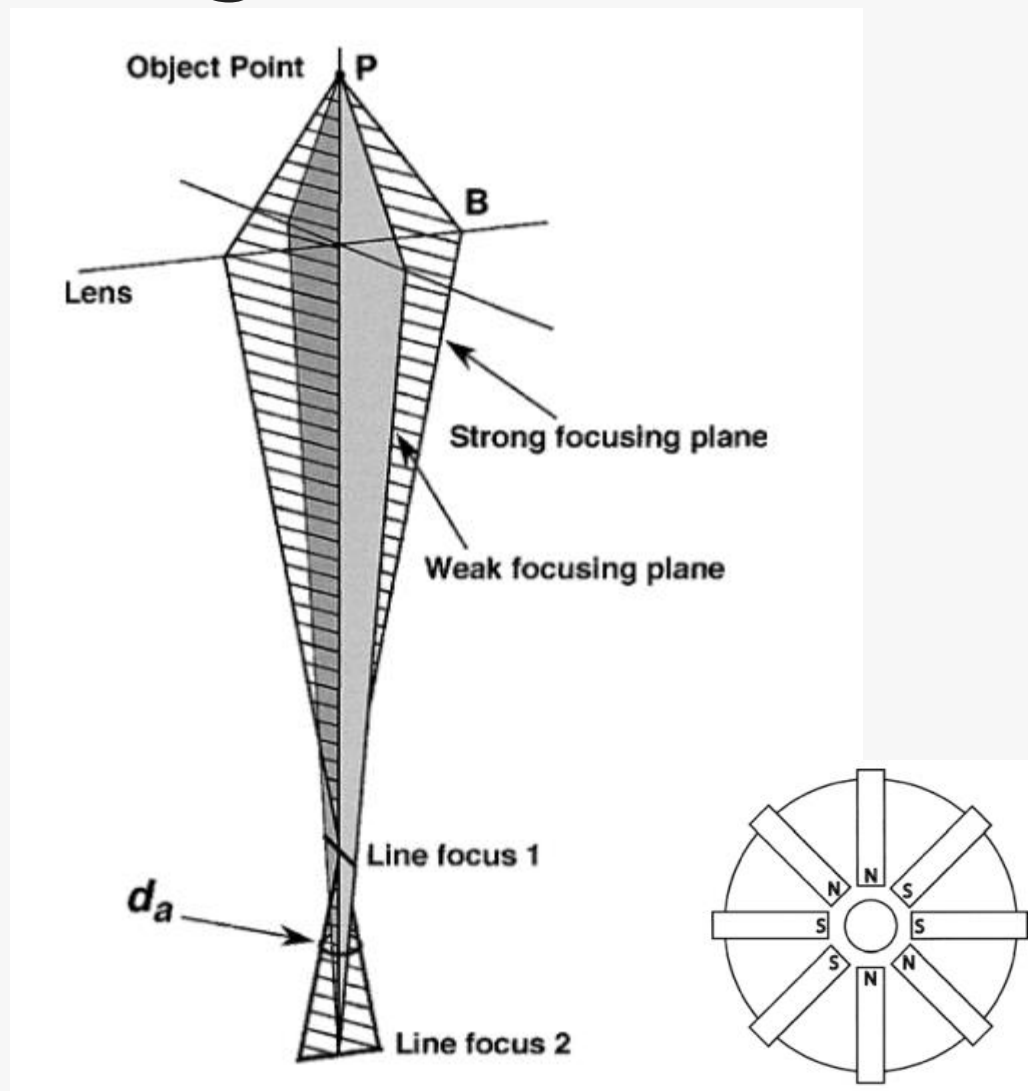
Almost prop to  $f$

• Chromatic aberration

$$d_c = C_c \alpha \left( \frac{\Delta E}{E_0} \right)$$

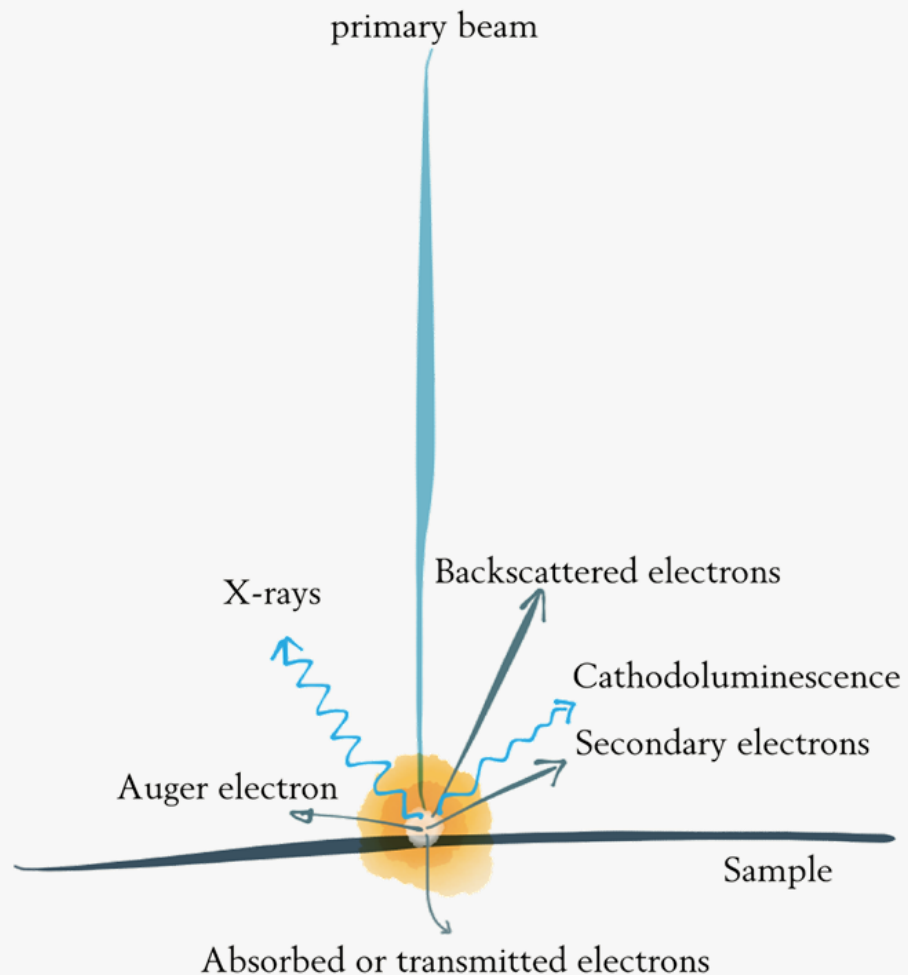


# Astigmatism



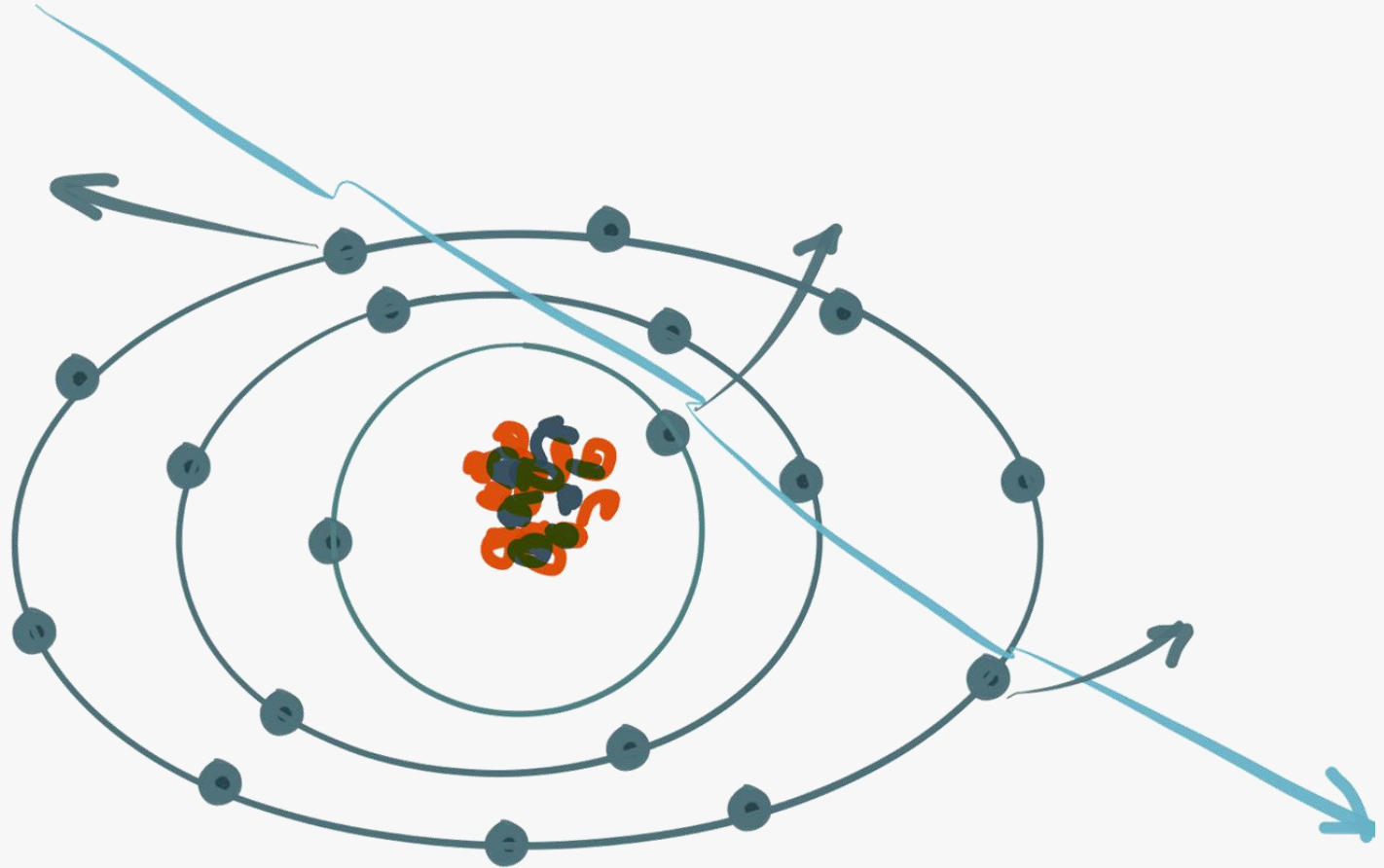


# Electron matter interaction



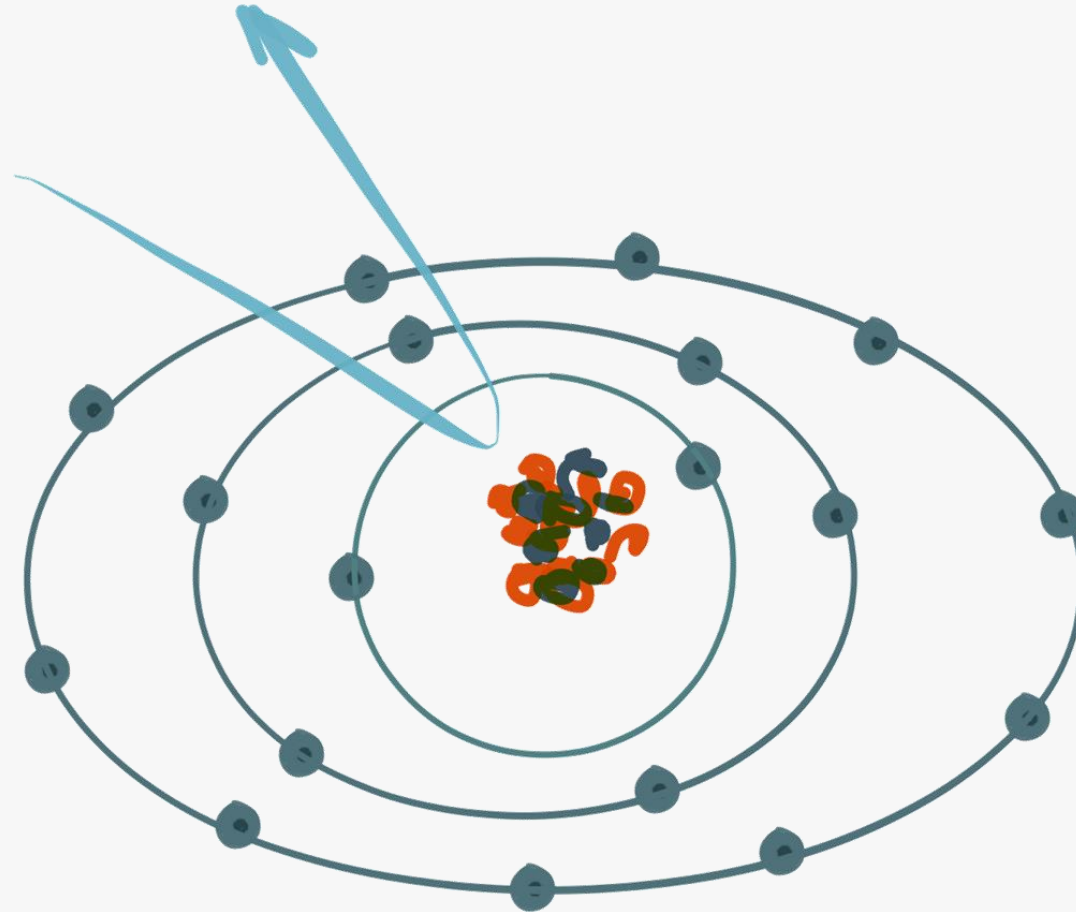
# Secondary electrons

- Non-elastic collision
- Electrons come from inside the atoms in the sample.
- Low energy
- Information about surface topography



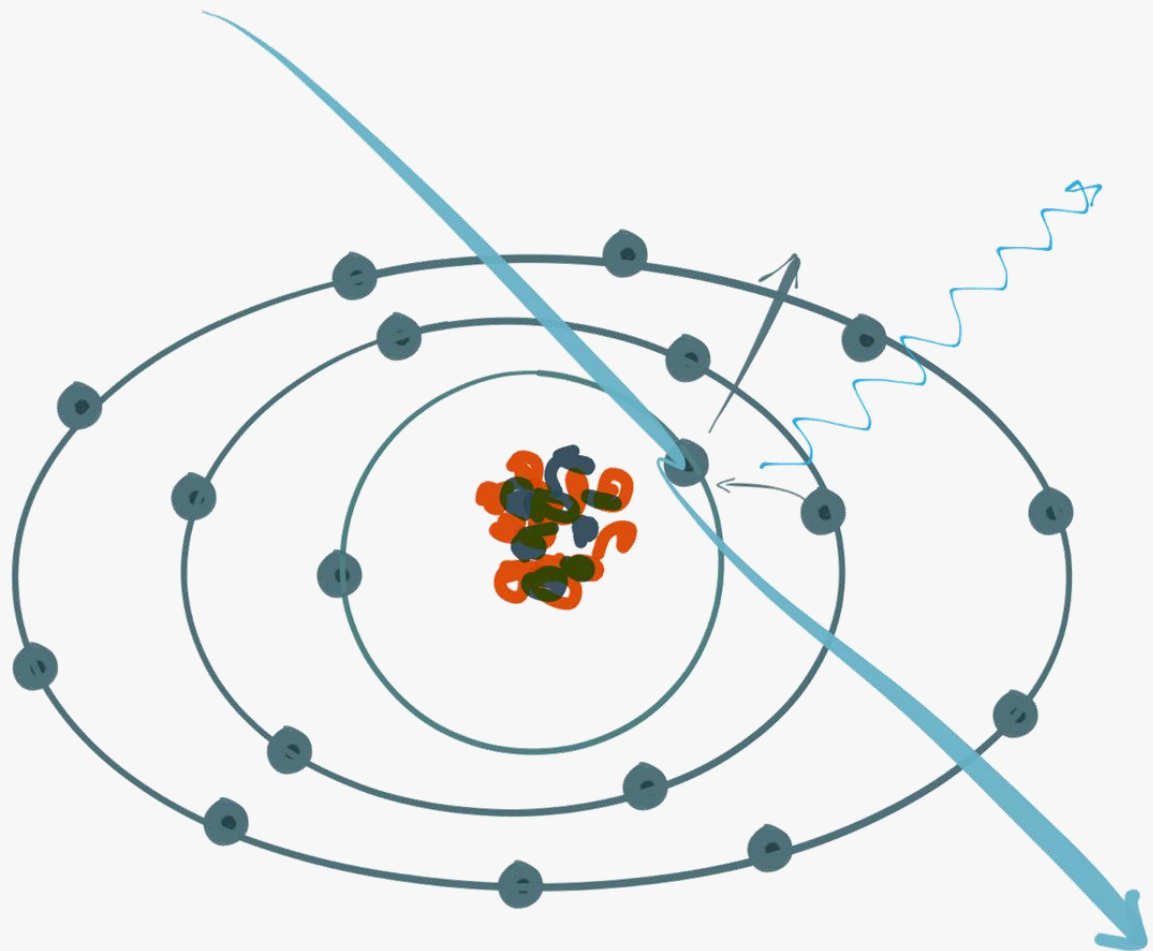
# Backscattered electrons

- (Almost) elastic collision
- Electrons come from the primary beam.
- High energy
- Probes deeper into the sample
- Some information about elemental composition



# X-ray emission

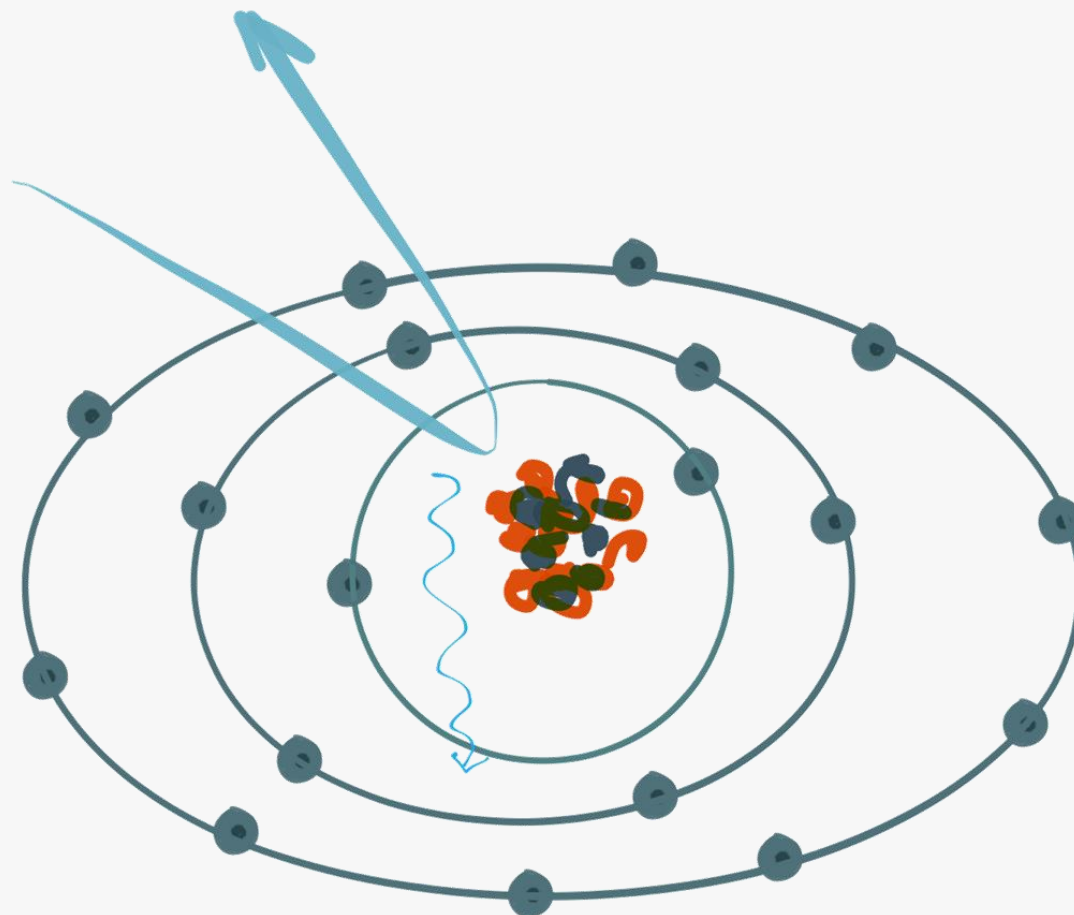
- X-ray emission sent out when an electron emitted from an inner shell and another outer electron fills the hole
- Specific elemental information.
- Basis of EDX.



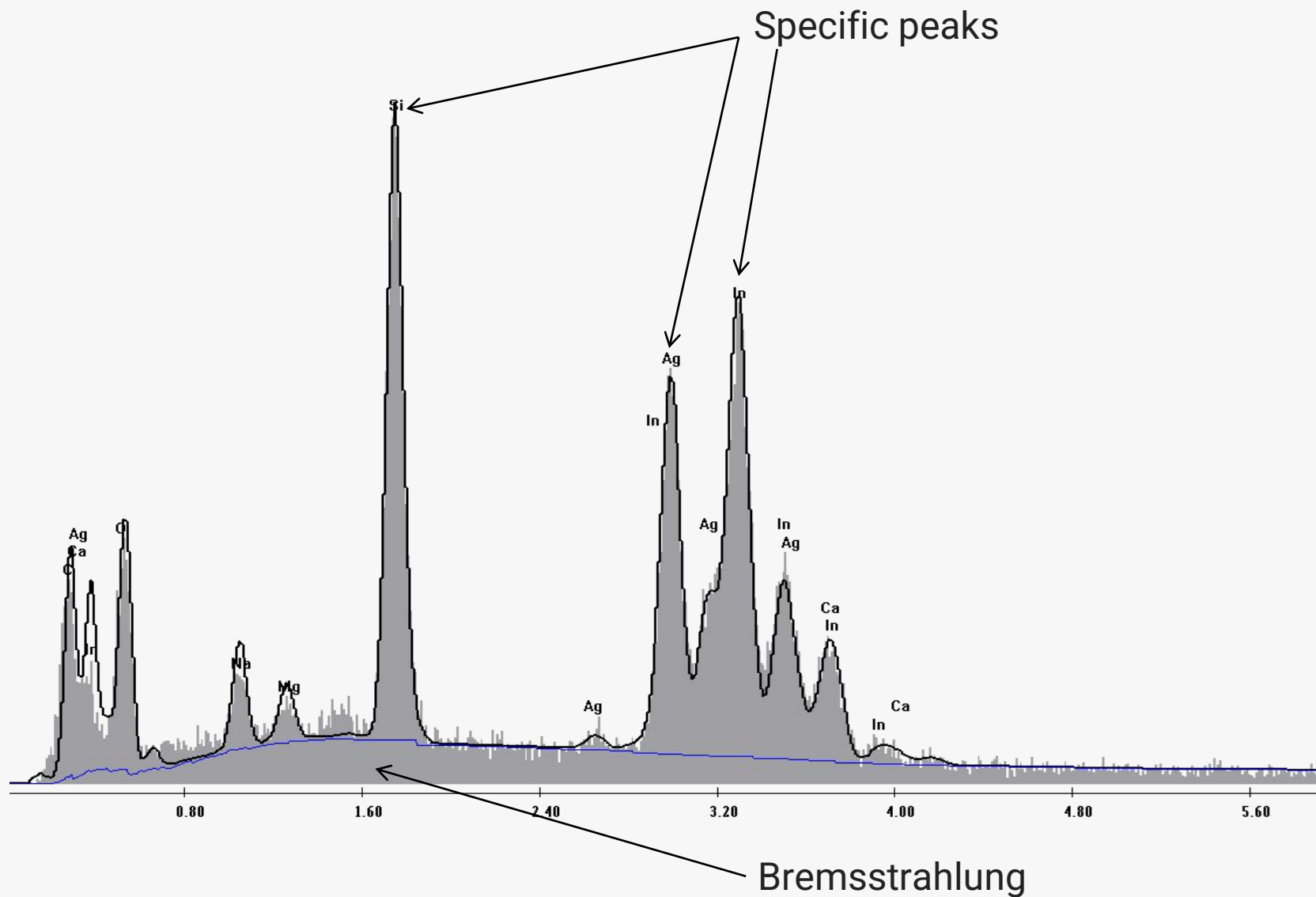


# X-ray emission (Bremsstrahlung)

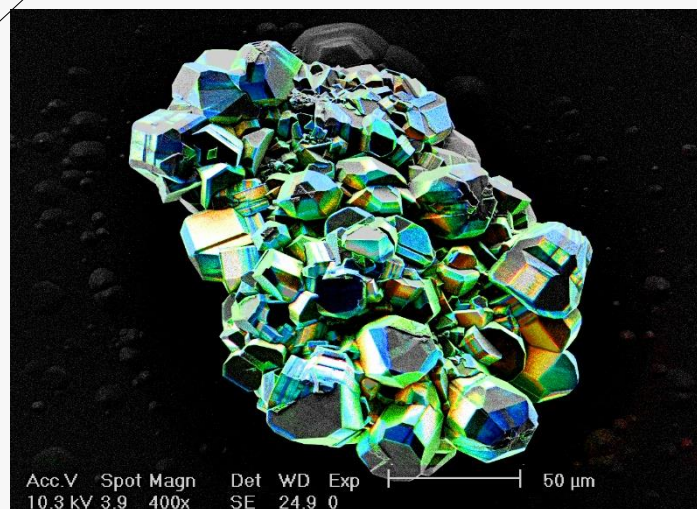
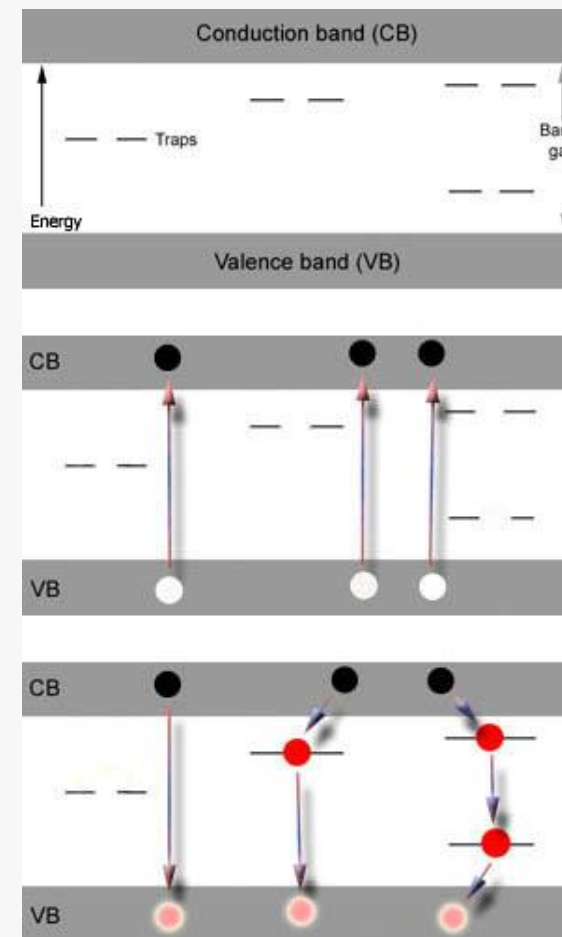
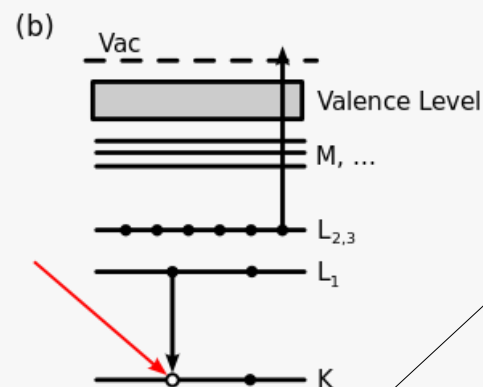
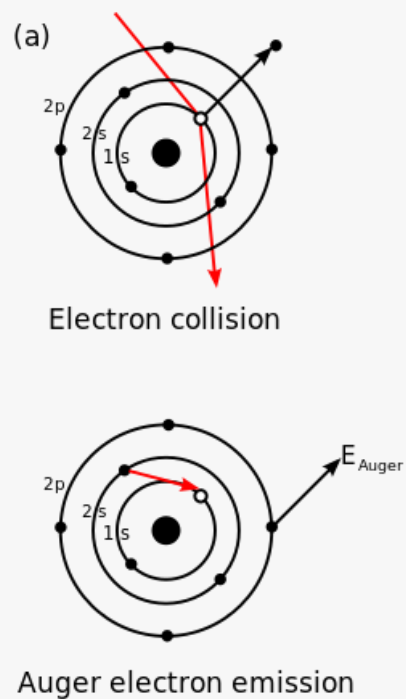
- X-ray emission sent out when an electron is accelerated.
- No elemental information.
- Forms background in EDX



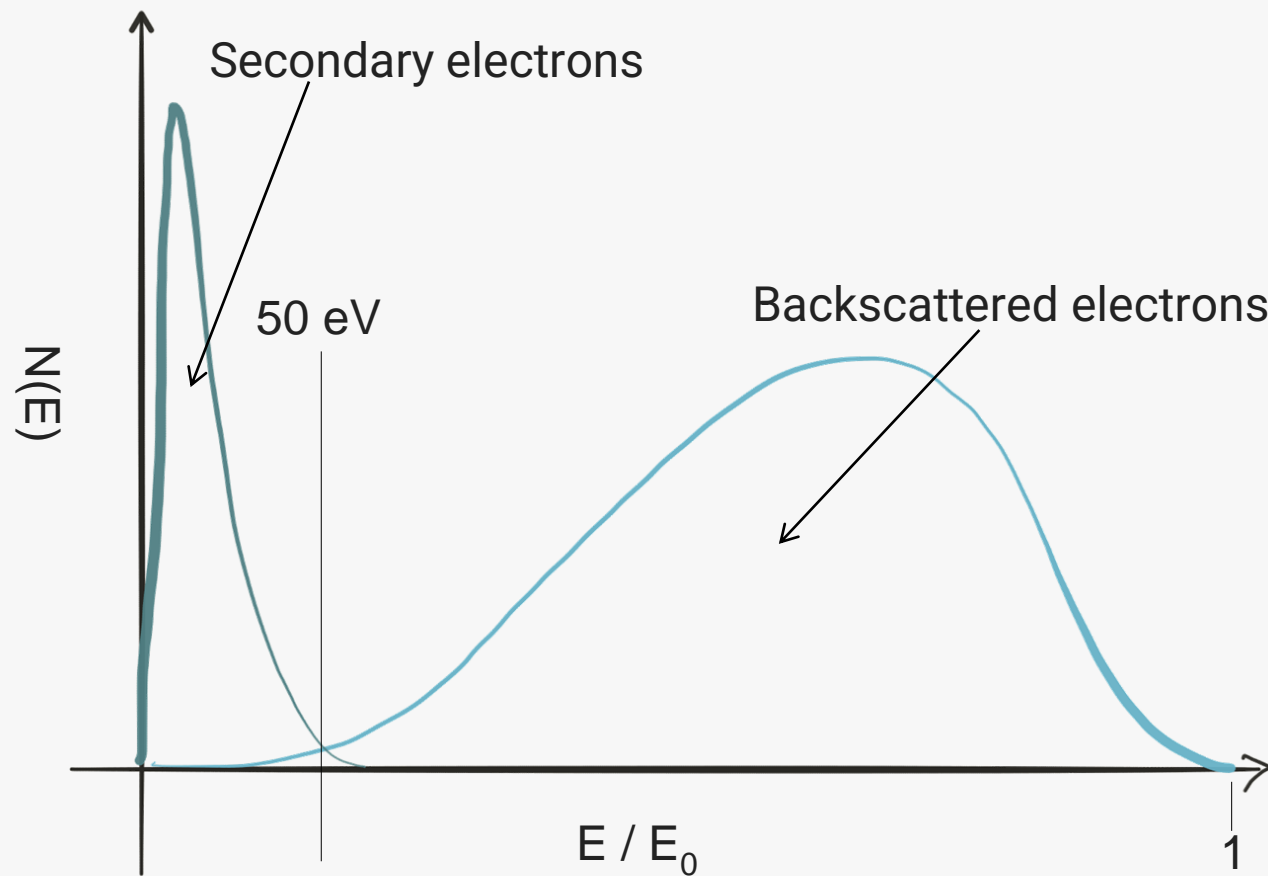
# X-ray emission



# Auger electrons / Cathode luminescence



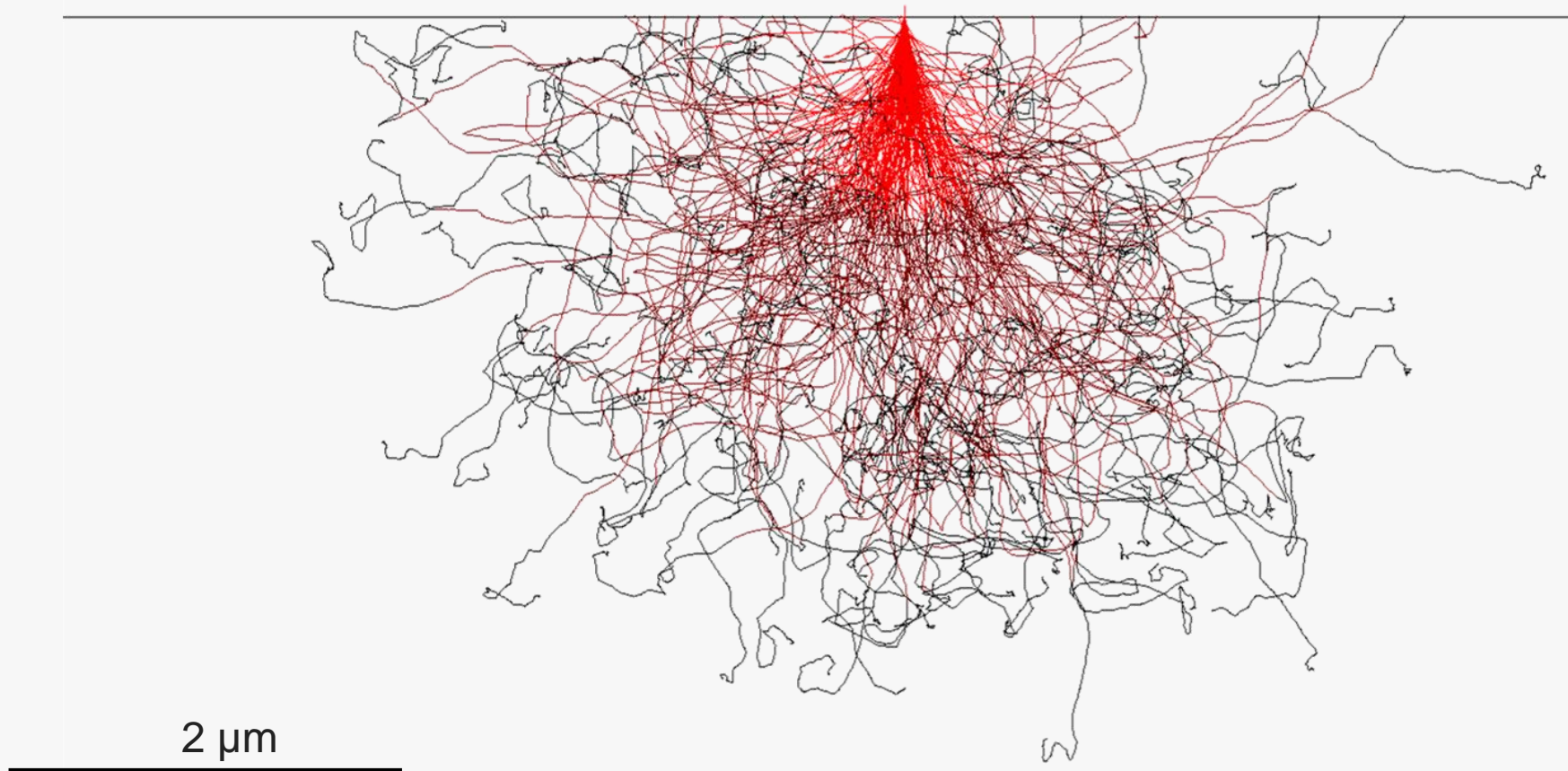
# Types of electrons?



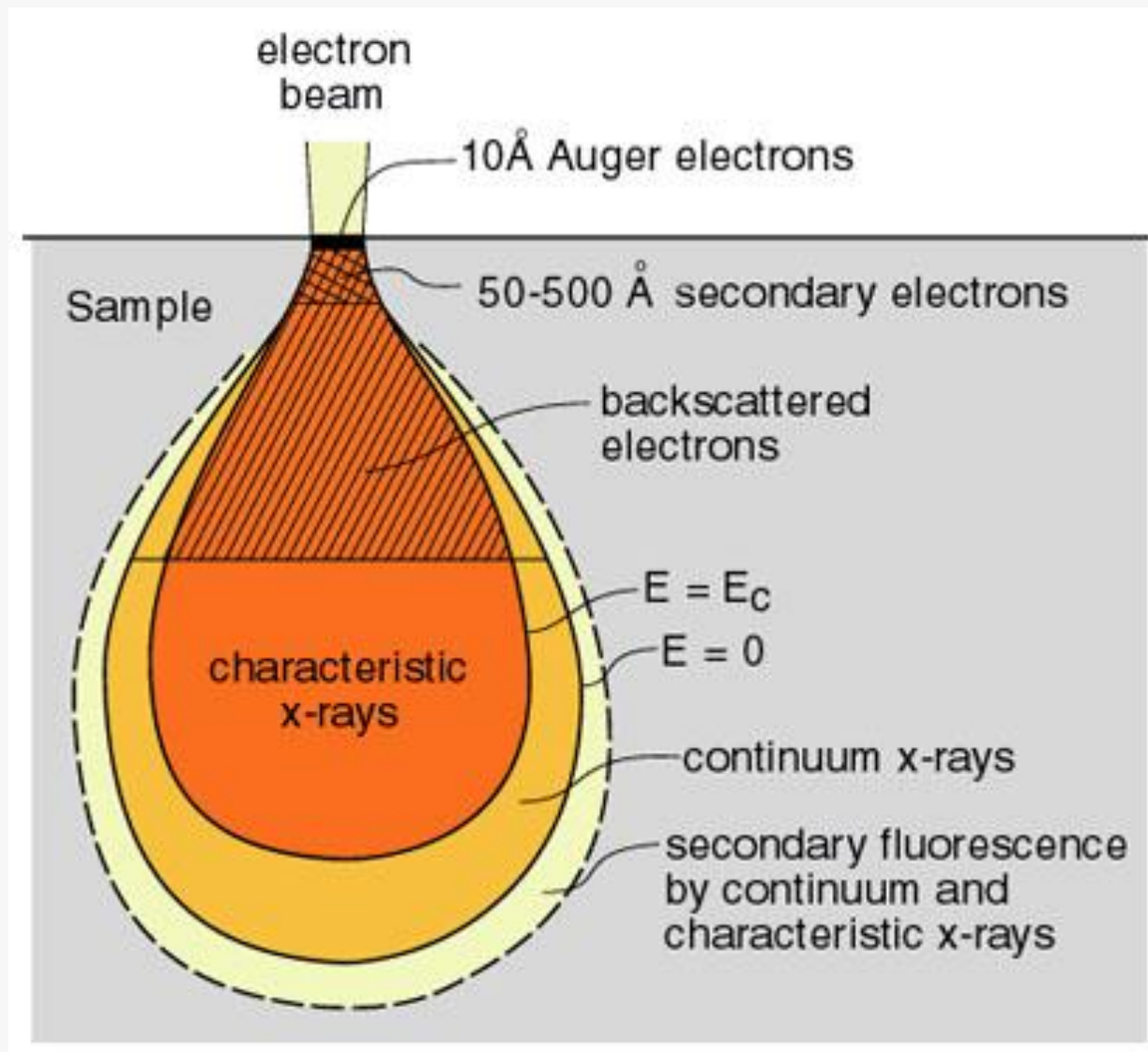


# Interaction volume

20 kV beam in Si



# Interaction volume

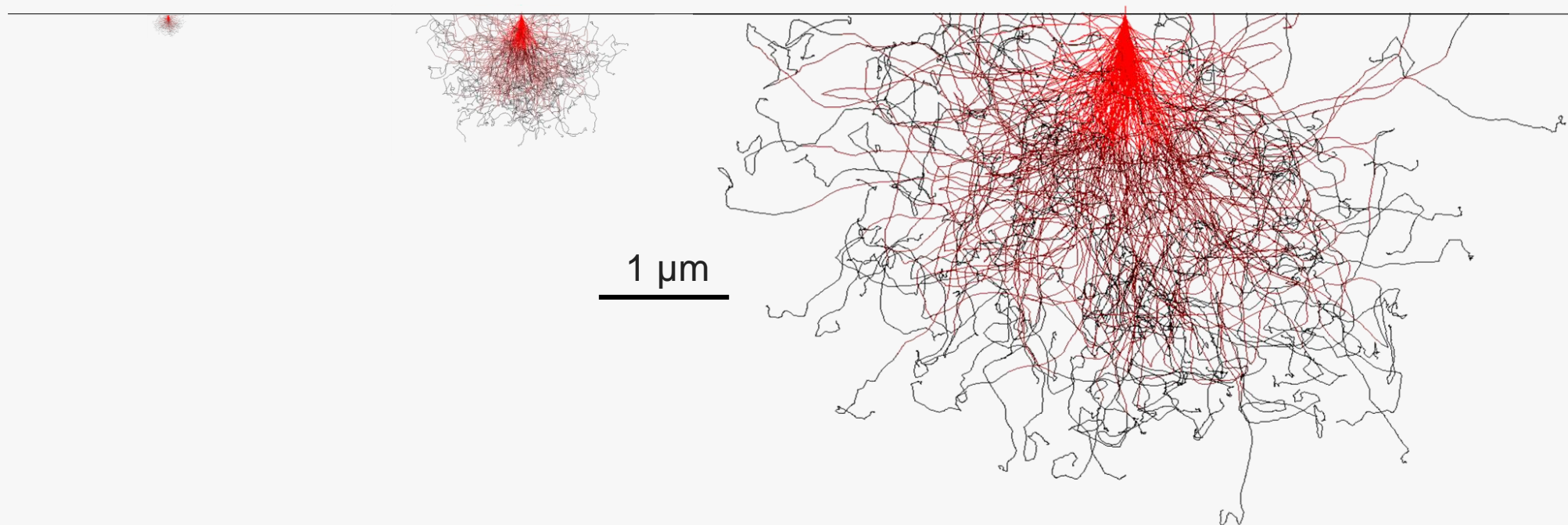


# Interaction volume

2 kV beam in Si

10 kV beam in Si

20 kV beam in Si

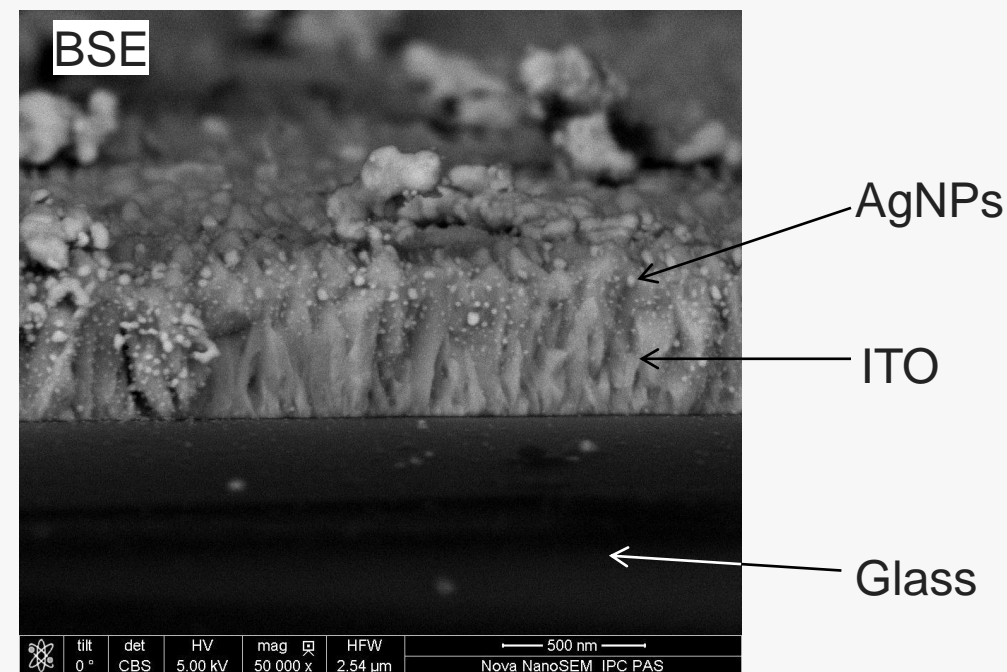
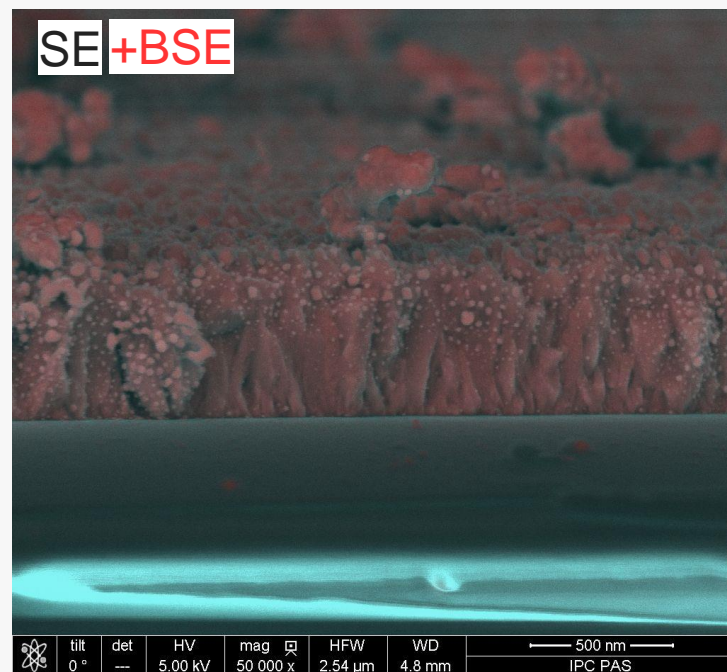
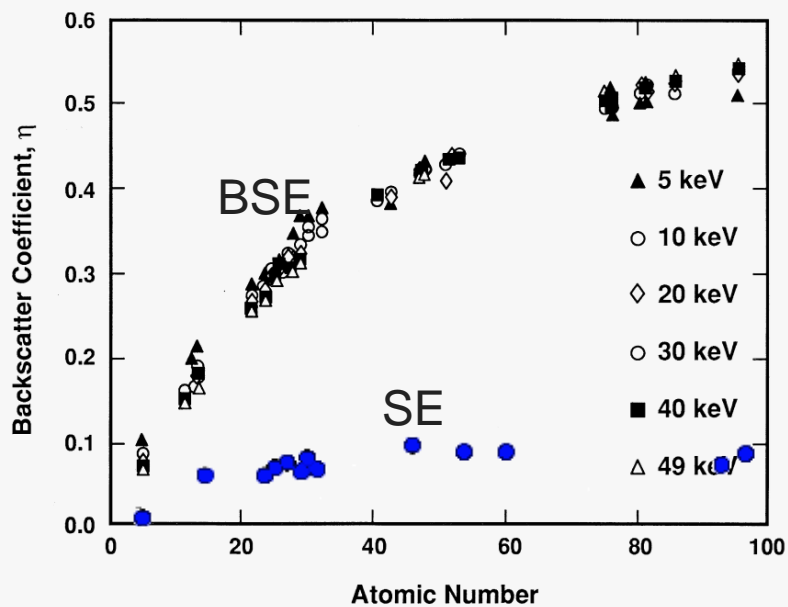


20 kV beam in SS

# Backscatter efficiency

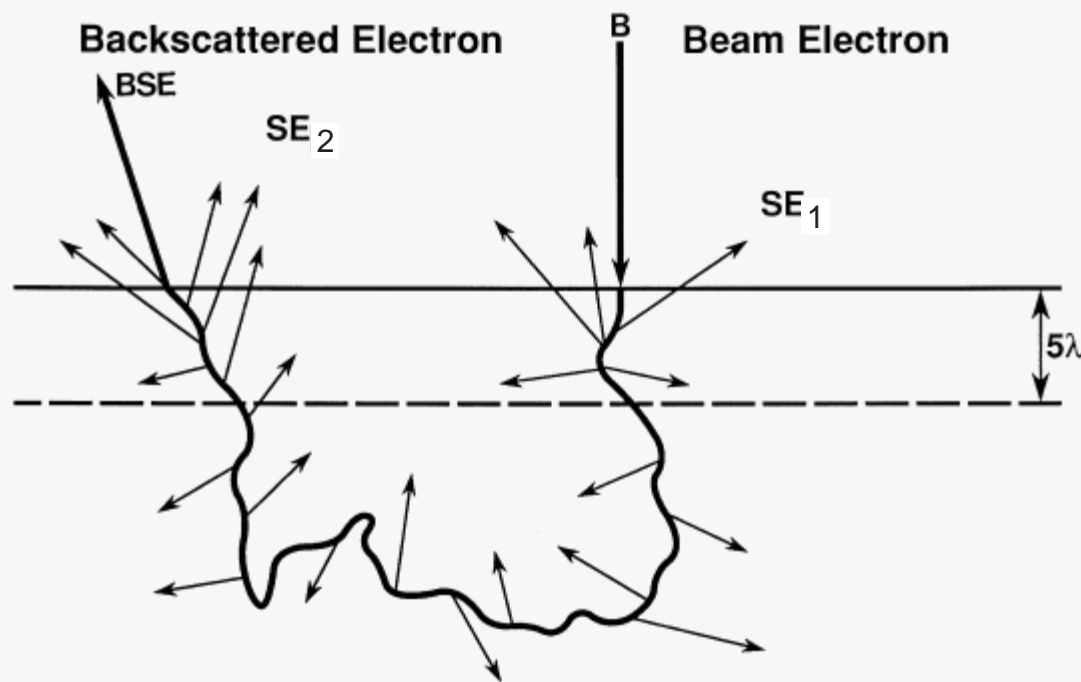
Backscatter efficiency is element dependent, but relatively insensitive to energy.

$$C = \frac{\eta_1 - \eta_2}{\eta_2} \quad \eta = \sum_i C_i \eta_i,$$





# Secondary electrons

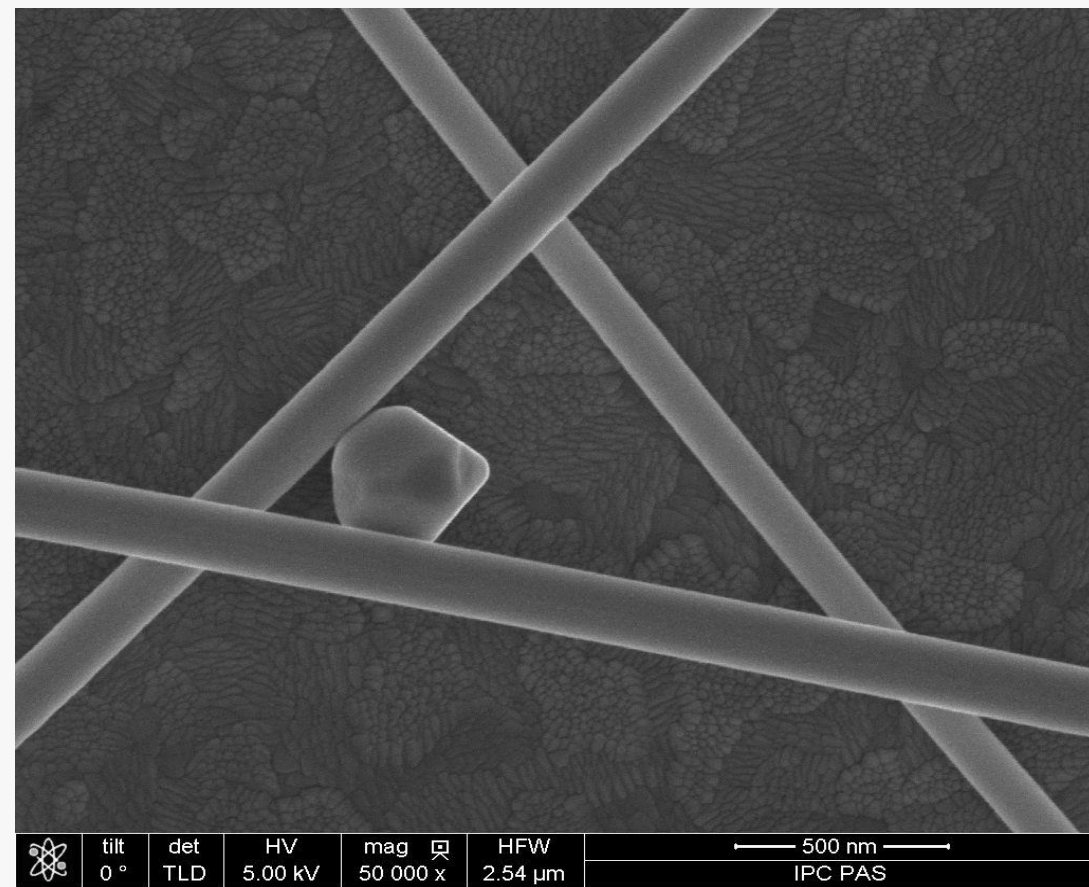
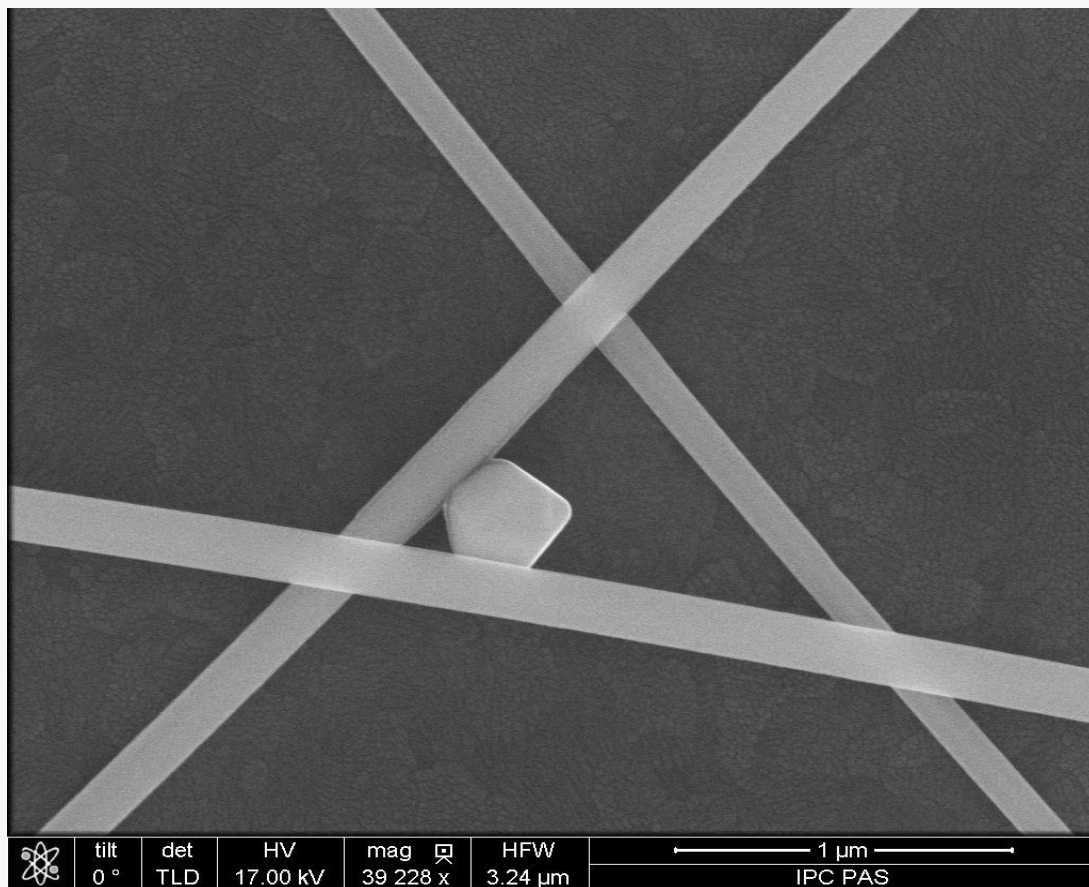


Secondary electrons are created both from the initial beam, and the scattered BSEs. Information about deep structures also in SE.

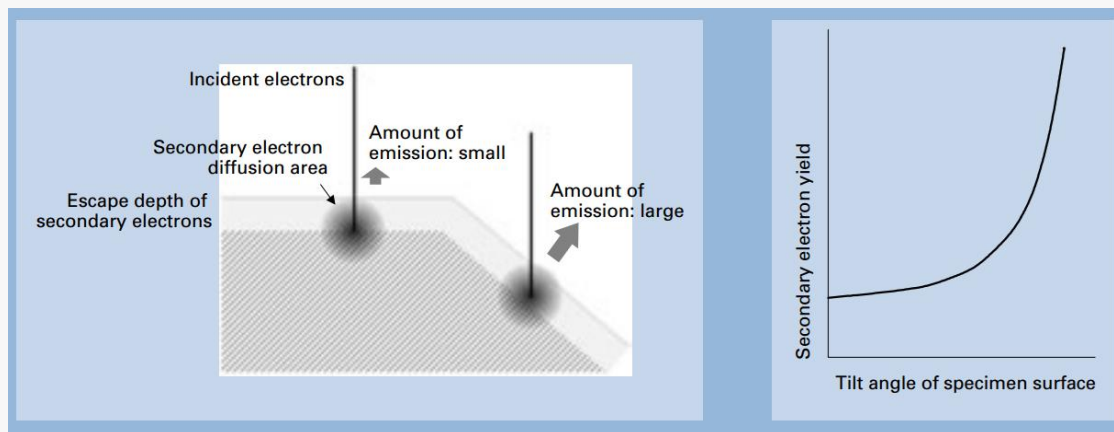
$\lambda \sim 1 \text{ nm}$  for metals  
 $\sim 10 \text{ nm}$  for insulators

# Secondary electrons

SE images of nanowires with different acceleration voltages.



# Secondary electrons



SE yield is strongly angle dependent.  
→ bright sides of structures

Edge effect also gives over-saturated edges.

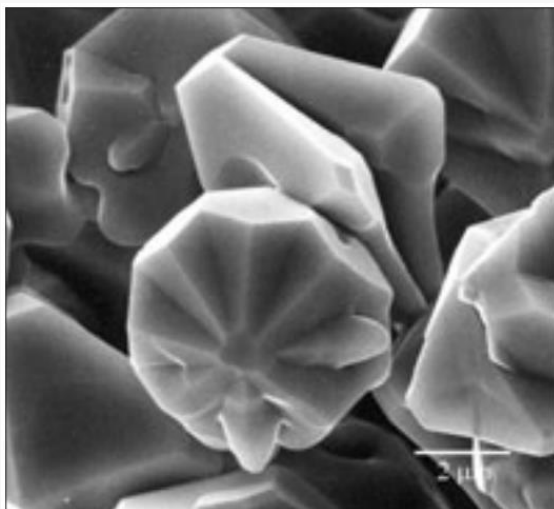
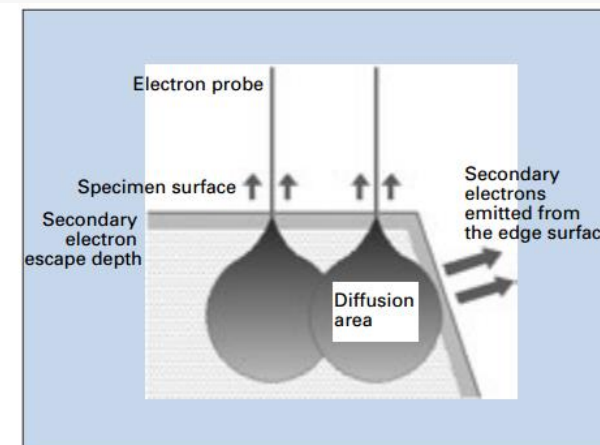
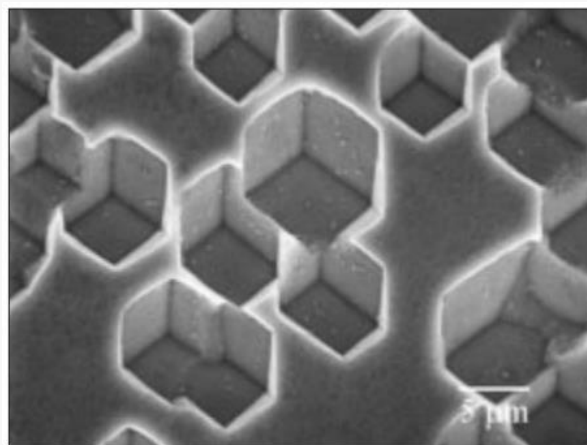
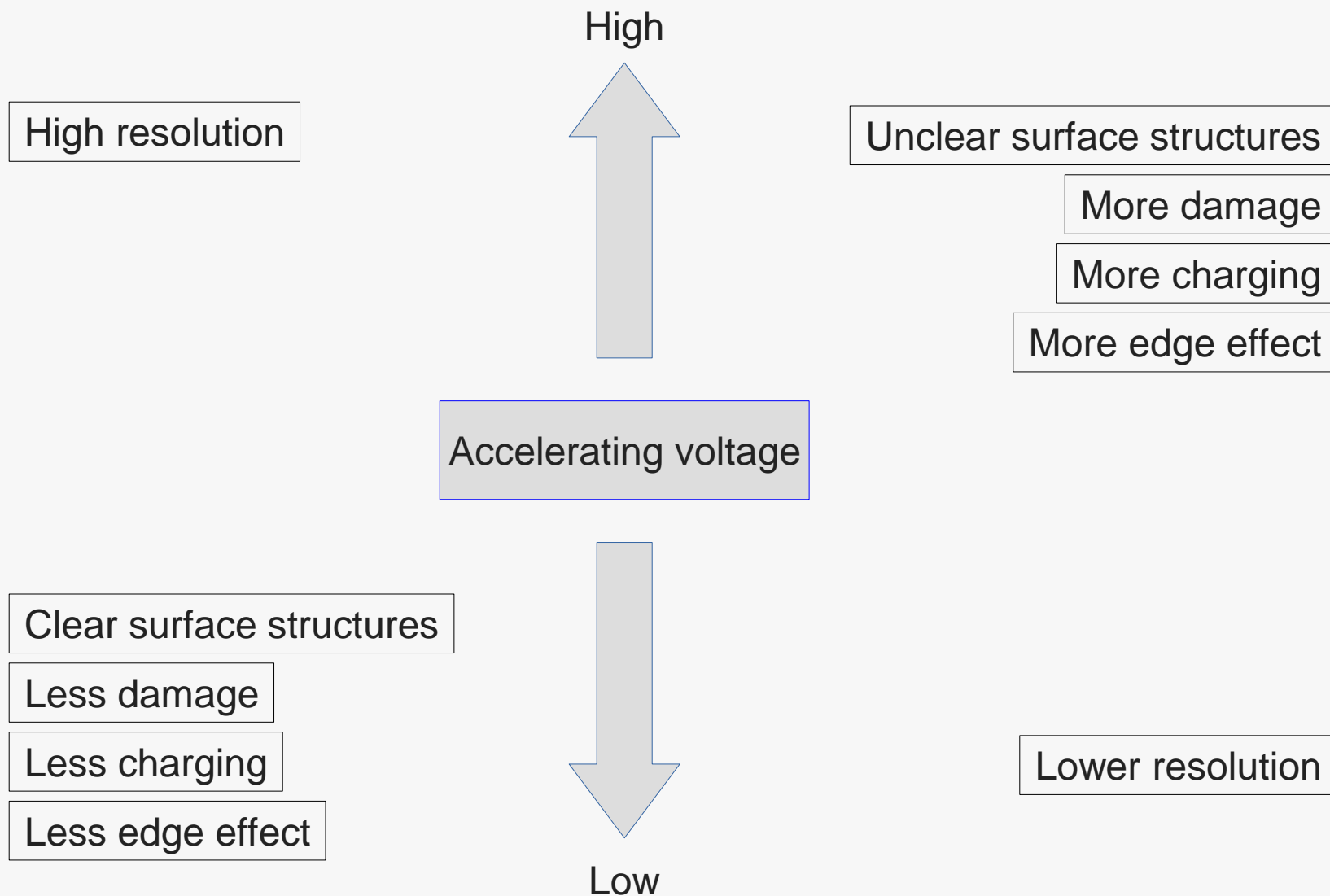


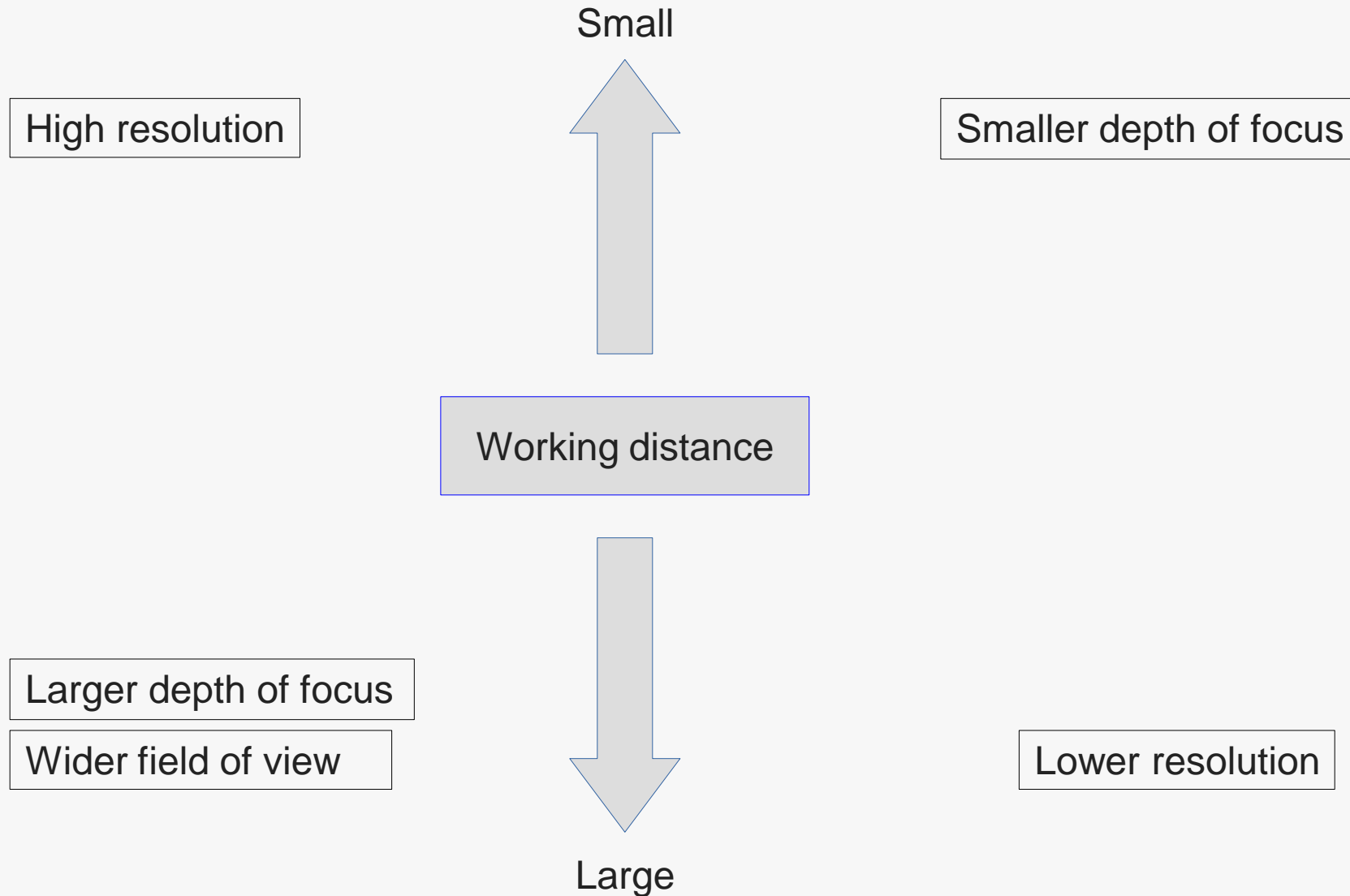
Fig. 15 Secondary electron image of tungsten oxide crystal.



# A game of compromises

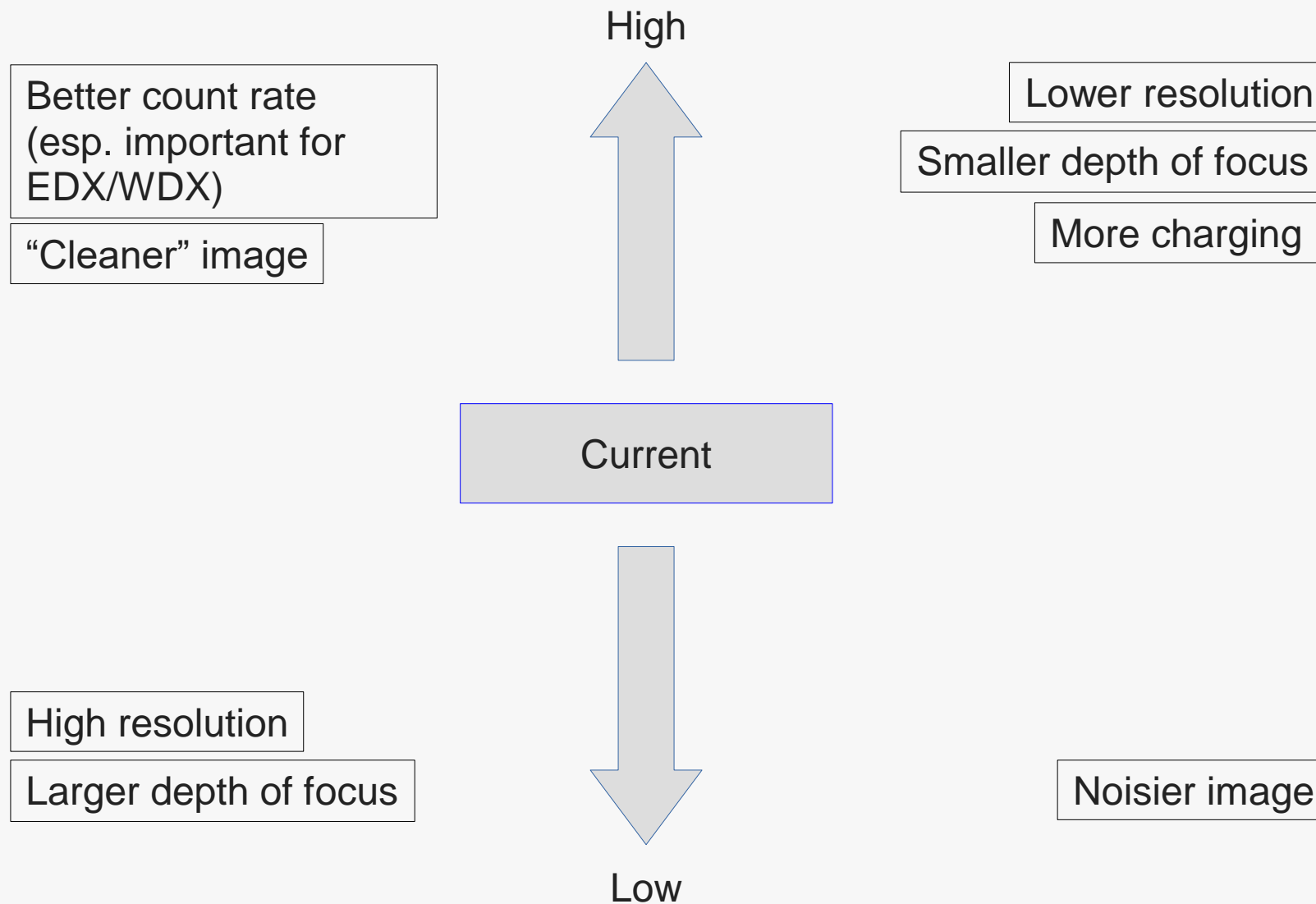


# A game of compromises





# A game of compromises



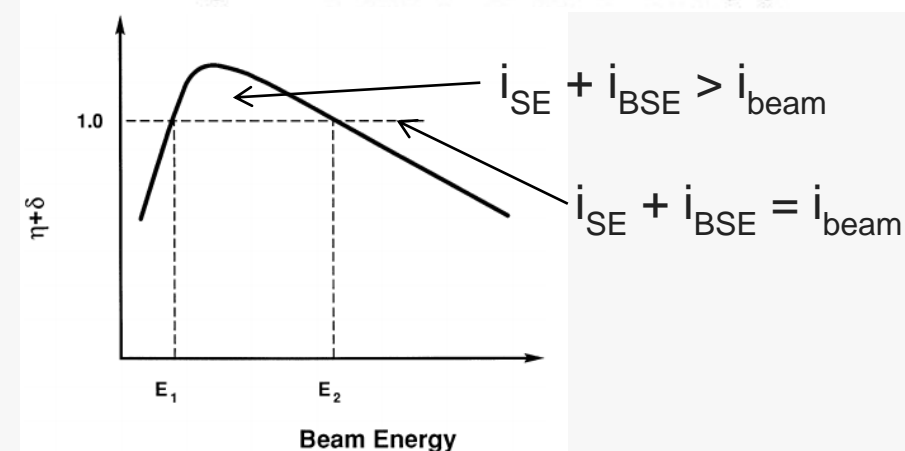
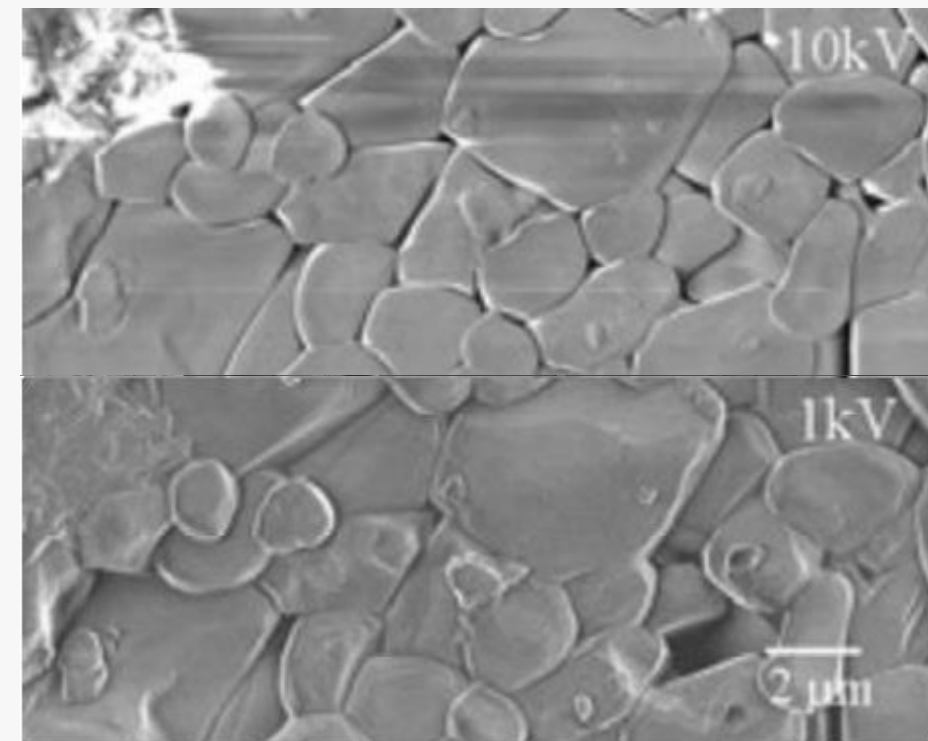
# Charging

Charging occurs when the sample, or part of the sample, is not sufficiently conductive.

- Anomalous contrast  
Too bright, too dark. Often changing over time
- Distortion

**Table 3.6.** Upper Crossover Energy for Various Materials (Normal Beam Incidence)

| Material           | $E_2(\text{keV})$ | Reference                   |
|--------------------|-------------------|-----------------------------|
| Kapton             | 0.4               | Joy (unpublished)           |
| Electron resist    | 0.55–0.70         | Joy(1987)                   |
| Nylon              | 1.18              | Joy (unpublished)           |
| 5% PB7/nylon       | 1.40              | Krause <i>et al.</i> (1987) |
| Acetal             | 1.65              | Vaz (1986)                  |
| Polyvinyl chloride | 1.65              | Vaz (1986)                  |
| Teflon             | 1.82              | Vaz and Krause (1986)       |
| Glass passivation  | 2.0               | Joy (1987)                  |
| GaAs               | 2.6               | Joy (1987)                  |
| Quartz             | 3.0               | Joy (1987)                  |
| Alumina            | 4.2               | Joy (unpublished)           |



# How to avoid charging?

- **Lower voltage**
- **Lower current**
- **Faster scanning & image integration**
- **Line interlacing**
- **Tilting the sample**
- **BSE instead of SE**
- **Low vacuum mode**
- **Coating the sample**

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